# Introduction to the Design of Full-Custom Front-End & Data Transmission ASICs\*

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- → Briefly read-out RO
- Briefly serializer SER
- → Briefly phase-lock loop PLL

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- Natural frequency concept ω
- Real-world examples:
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- Photodetectors vs photon counters
- Position-sensitive detectors
  - Resistive charge division
  - Discrete array of elements
- Time-resolved detection

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- → Transconductance of a transistor g\_
- Evolving a single-stage amplifier into a real-world application

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  - → Formation of an **nMOS** transistor
- VLSI design flow
  - Parasitic extraction
- → Real-world ASIC examples

### Radiation Tolerance Issues

- Definitions:
  - Single event upset, analog single event transient, latch-up
- Simulating radiation effects on analog circuits

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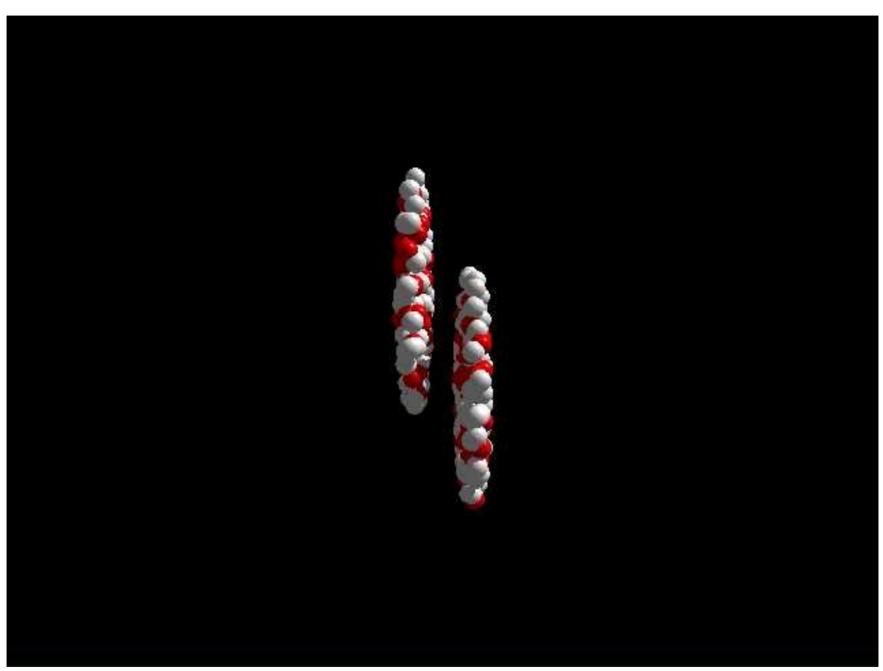
### Motivation for the TOC

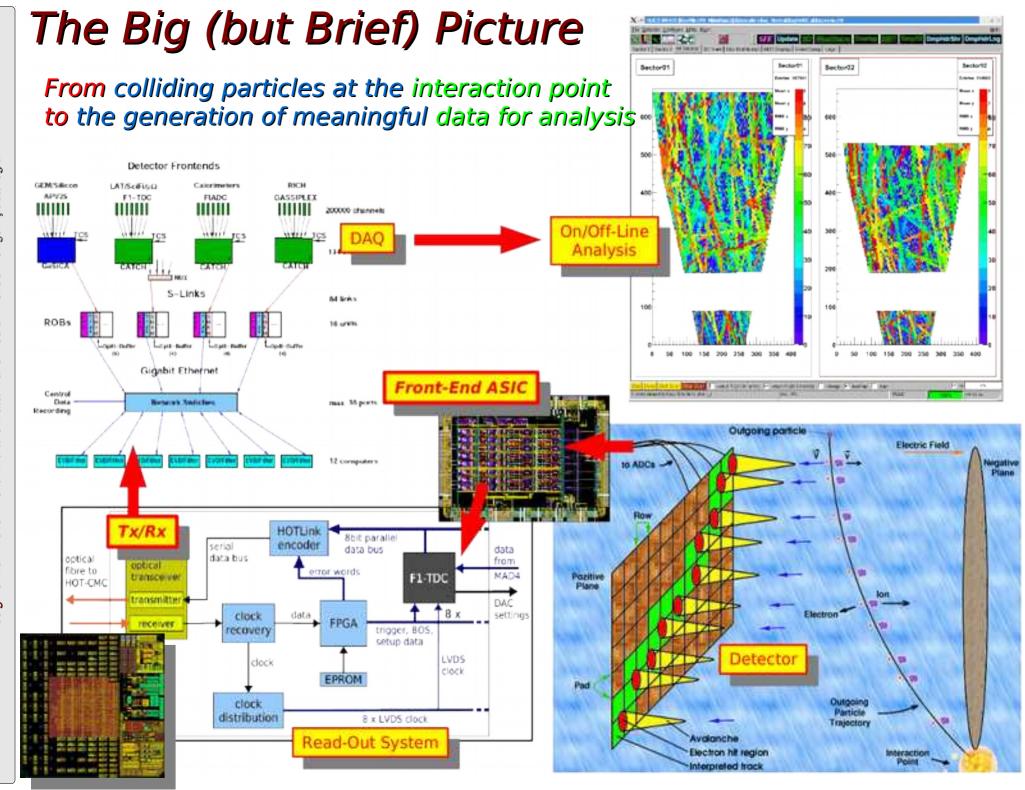
Composition within the ISOTDAQ curriculum

- One of the official goals of the school is to "expose the participants to a maximum variety of topics"
- What comes just after the "detector" is the first link of the DAQ chain
- Therefore this lecture will try to deliver:
  - → an *intuitive approach* to what is listed in the **TOC**
  - → without providing "dry and ugly" math phrases
- This lecture will have no specific hands-on laboratory session in the current program of the school
  - → However it will **always** be there at the lowest level of all the laboratory sessions you will attend
- The pages will contain **enough amount of text** necessary for you **NOT** to need a lecturer in order to understand the slides at home (naively assuming that you will refer to this lecture in near future)
  - → Therefore please be aware of the above fact, in case you start feeling that the pages are a little bit **overloaded**

# An Ordinary Heavy Ion Collusion

Heavy ions at the center of ALICE detector; a short movie of 5 ns

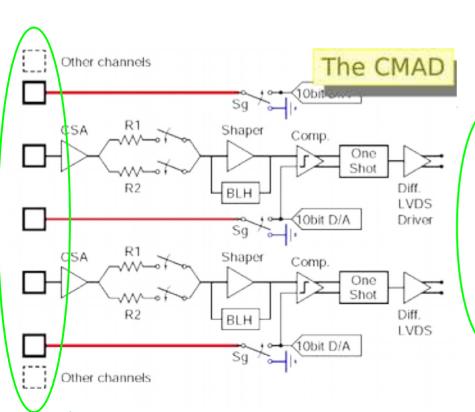


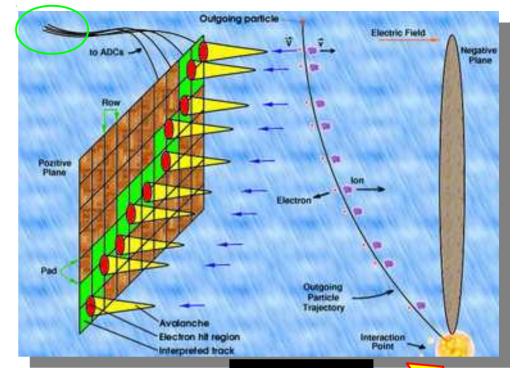


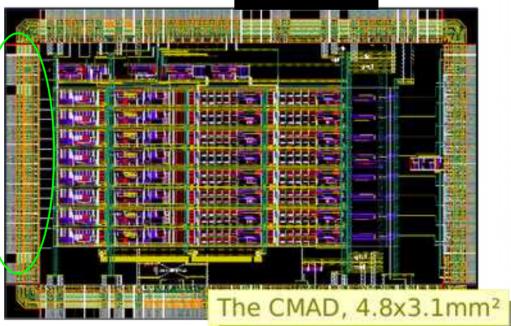
# **Briefly Front-End**

First interpretation of detector data

- Integrate the charge as a pulse
- Shape this pulse
- 1) Compare pulse height to a threshold
  - Higher ? Yes: No
- 2) Digitize the pulse for further processing
  - → Digital filters, corrections, etc.
- Send the result to read-out



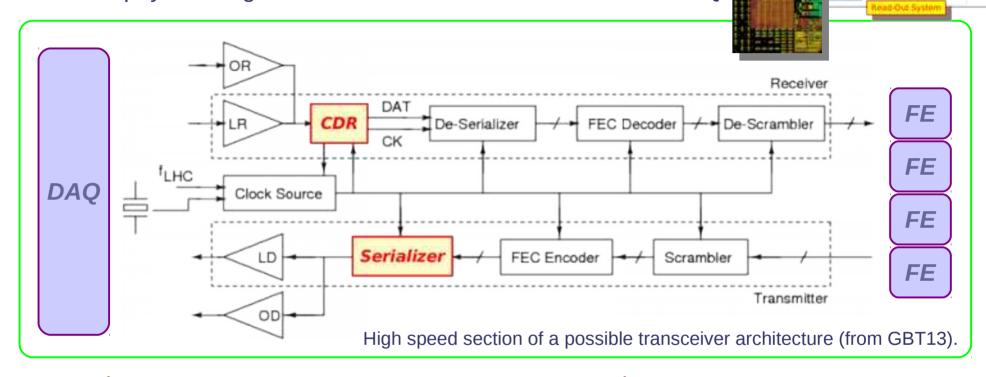




# **Briefly Read-Out**

How to get data from FE and deliver to DAQ

- Add header/trailer to the data created by the detector FEs
- Combine payload fragments into frames to be transmitted to DAQ



#### Receiver

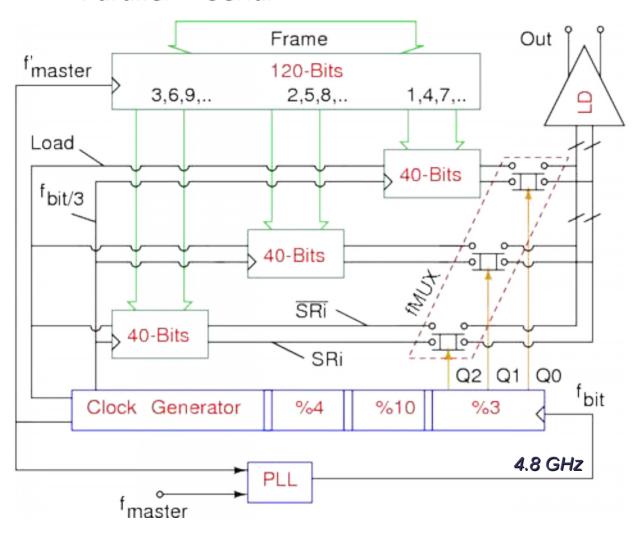
- → Receive laser light representing serial data from fiber
- Check FEC code and correct errors (if possible)
- Parallelize data
- → **Deliver** data to the next stage e.g. FE

### Transmitter:

- Get data from FE
- Calculate FEC and add to frame, increasing resistance against transmission errors
- → Serialize parallel data
- → Drive a laser diode over fiber to DAQ

# Briefly SER

Parallel → Serial

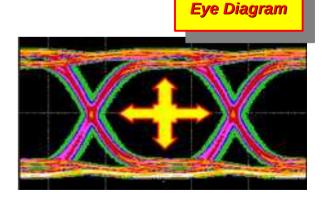


# SR0 SR1 SR2 Q0 Q1 Q2 Out

DAO

### **Operation:**

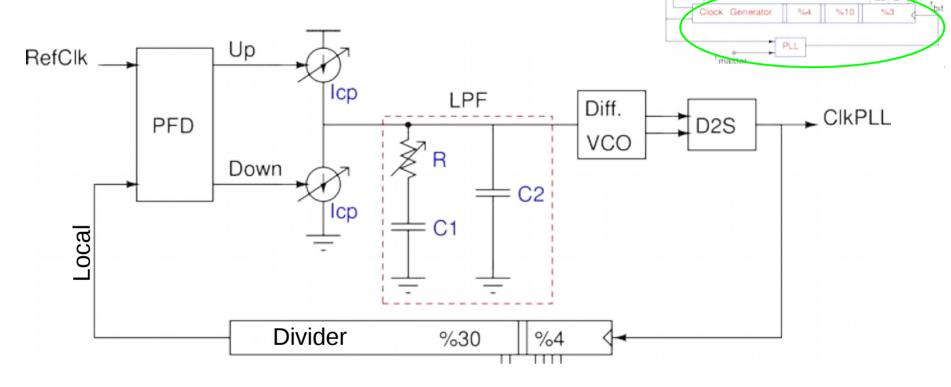
- @ rising edge of f<sub>MASTER</sub>, load 120-bit-wide frame into input register (40 MHz)
- @ rising edge of Load, divide the frame into 3 40-bit-wide words (40 MHz)
- @ rising edge of f<sub>BIT/3</sub>, right shift 30-bit-wide words sequentially (1.6 GHz)
- After every shifting, multiplex the right bit to output (4.8 GHz)



# Briefly PLL

### Phase-lock loop

- Locking a clock to a (pseudo) periodic signal
- ClkPLL is what we we generate locally and RefClk is the reference to be tracked or to be locked to



master

fbit/3

40-Bits

2,5,8,

- Measure the rising instant timing difference between RefClk and ClkPLL by the phasefrequency detector (PFD)
  - Generate correction commands depending on this measurement (Up, Down)
- Correction commands control the charge pump (Icp) pumping/sinking current into/from the filter capacitor, varying the control voltage for the Voltage Controlled Oscillator (VCO)
  - Gradually, the timing error of the two signals at the inputs of the PFD would vanish (ideal locked condition)

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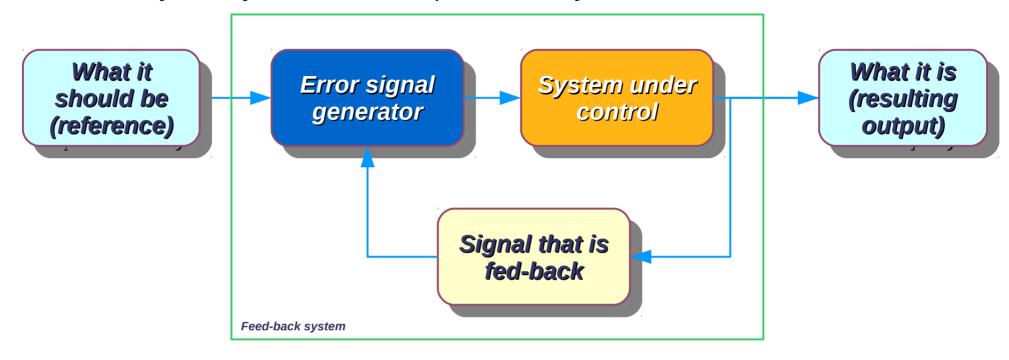
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### Feed-Back

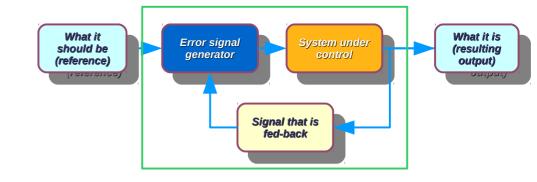
Actually a very familiar concept from daily life



- Aim, is decreasing the difference (the error signal) between the reference and the output
- How ? For each cycle:
  - → A **portion of the output** is fed-back. Make the system be **sensitive** to a portion of what it outputs
  - → Measure the difference between the reference and what is fed-back (only a portion of the output)
  - Depending on the difference, an error signal is generated which in turn causes a correction step to be taken controlling the system under control
  - Repeat the cycle

### Feed-Back

Actually a very familiar concept from daily life



- Whistling or playing an instrument ?
  - → How do I know what I play is "Do" but not "Re"?
  - → Does it make sense to say "I whistle **better** than you"?
  - → What happens when I try to find the right guitar solo for an existing song?
- Drinking a glass of water ?
  - Adjust the angle & position of the glass accordingly to keep the water flow as it is necessary?
  - Remember the childhood: sometimes the water gets dropped to the ground accidentally (What is the failure mechanism?)
- Walking and biking ?
  - → How do I decide the frequency of my steps not to fall down or to be able to reach somewhere?
  - What about walking or biking when drunk? (What is the failure mechanism?)
- Ruling a country ?
  - → Can "referendum" be a term borrowed from the control theory?
  - → How come politicians of the same ideology can decide in substantially different manners ? < Questionably ignoring corruption :D >

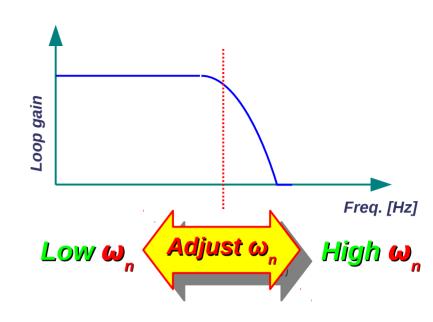
#### Feed-Back What it What it is System under should be (resulting generator control (reference) output) Natural frequency concept Signal that is fed-back Corner 100% Correct answers [%] Success $T(s) = \frac{\omega_n^2(\tau s + 1)}{\frac{s^2}{V} + 2\xi s \frac{\omega_n}{V} + \frac{\omega_n^2}{V}}$ Decreasing success How frequent the questions are asked [Hz] ω

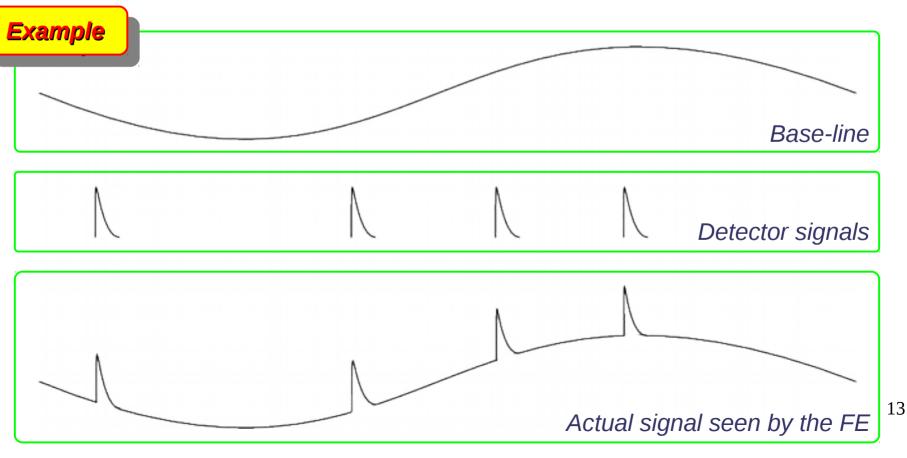
- An imaginary system answering questions asked continuously
- Plot (both logarithmic scale) the success level within a certain time window as a function of frequency of questions asked (transfer function)
- If the questions are asked slow enough, the system answers all, thus 100% success level
- Once the questions start to be asked faster, the system starts failing answering all, thus transfer function begins going down
- Corner is at the natural frequency of the control loop where the system starts impairing significantly

### Feed-Back

Choosing for what to be sensitive

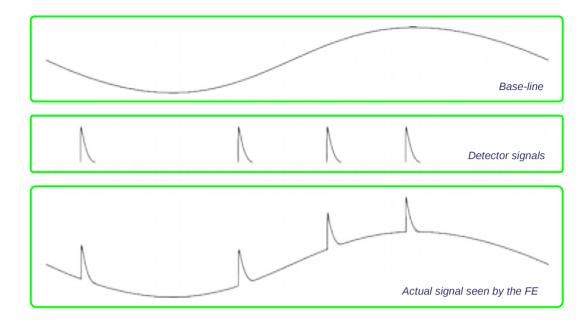
- Low ω<sub>n</sub> → Sense slow variations
  - Loop acts on slowly varying signals
  - → Narrow bandwidth slow loop
- High ω<sub>n</sub> → Sense fast variations
  - → Loop acts on rapidly varying signals
  - → Wide bandwidth fast loop

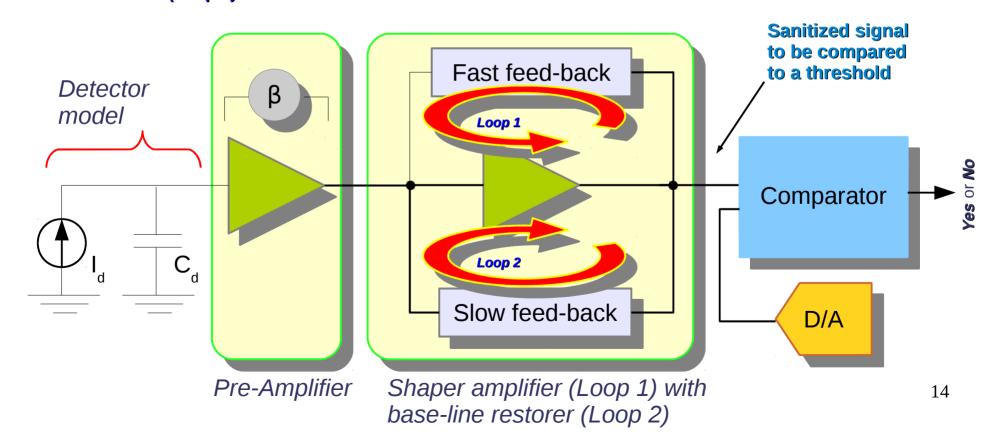




# Example Binary read-out

- Requires stable base-line
  - Which varies slowly
  - → A narrow loop bandwidth is needed (Loop 2)
- Requires a fast signal shaper
  - Which varies rapidly
  - → A wide bandwidth is needed (Loop 1)

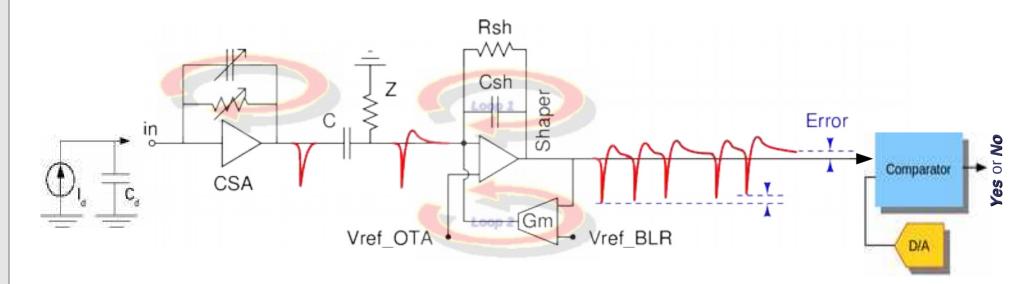


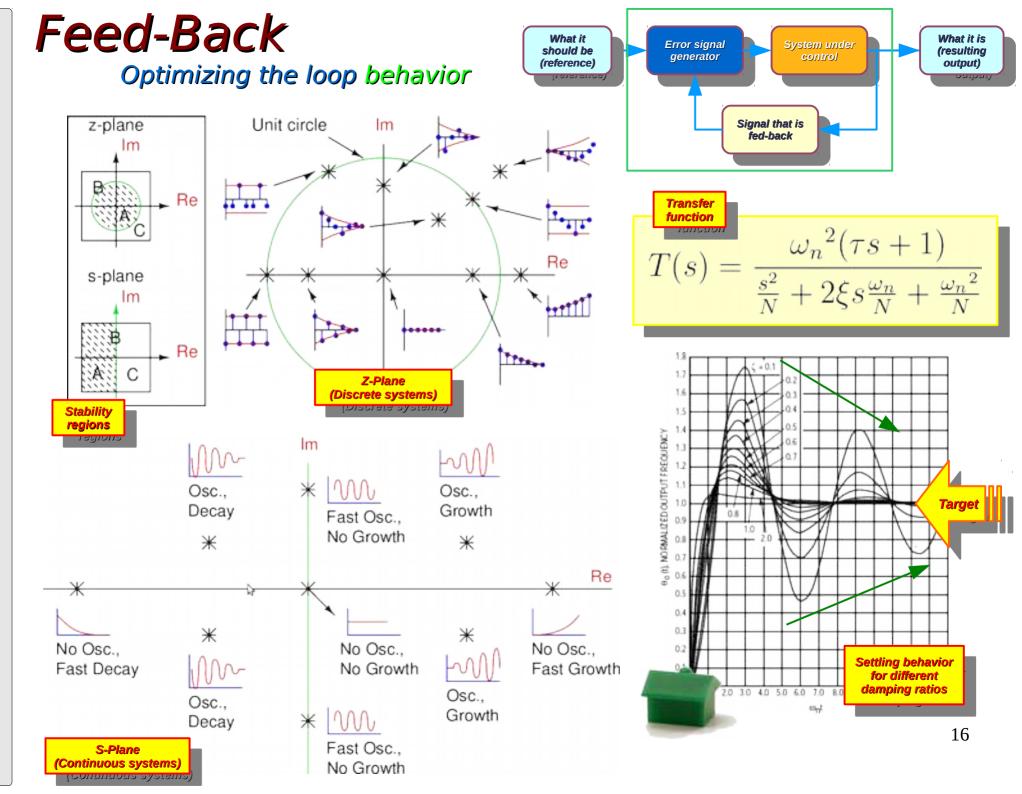


# Real-World Example

Binary read-out for time-over threshold measurement

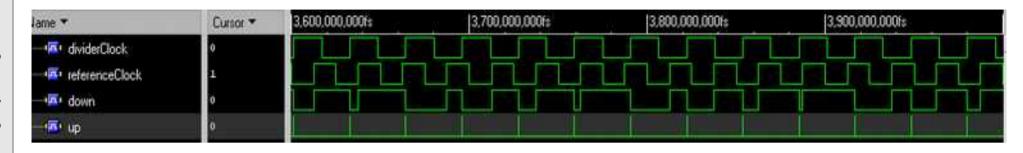
- Random detector pulses with a few MHz frequency; then...
  - How fast is the fast loop?
  - How slow is the slow loop?
- Depending on the read-out speed and the operating environment, parameters are optimized
  - → Natural frequencies and gains of the loops, rise/fall-times, etc.
  - Settling behavior, radiation tolerance, damping ratio, power, etc.
  - → Circuit footprint, robustness, redundancy, channel efficiency, etc.

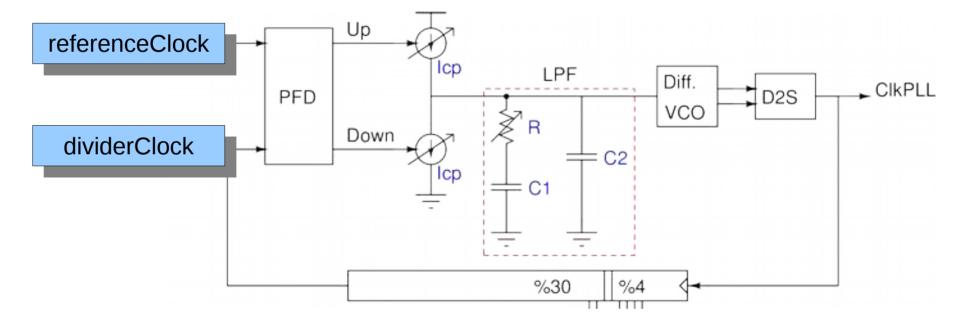




# Simulation Movie Quiz

Remember the PLL



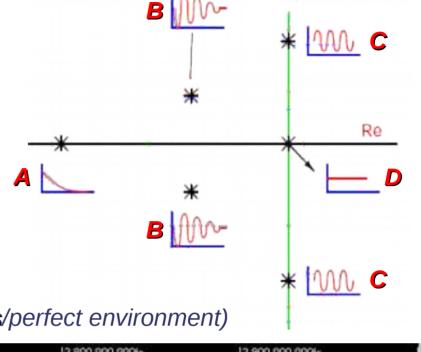


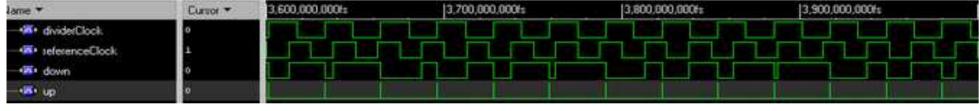
- Slow down the VCO, if it is too fast with respect to the reference
- Speed up the VCO, if it is too slow with respect to the reference

# Simulation Movie Quiz Different loop behaviors

- See the movies and associate the behavior to the poles on the s-plane (complex plane)
- Use your intuition

? - Slow-loop with low damping ratio (noiseless/perfect environment)

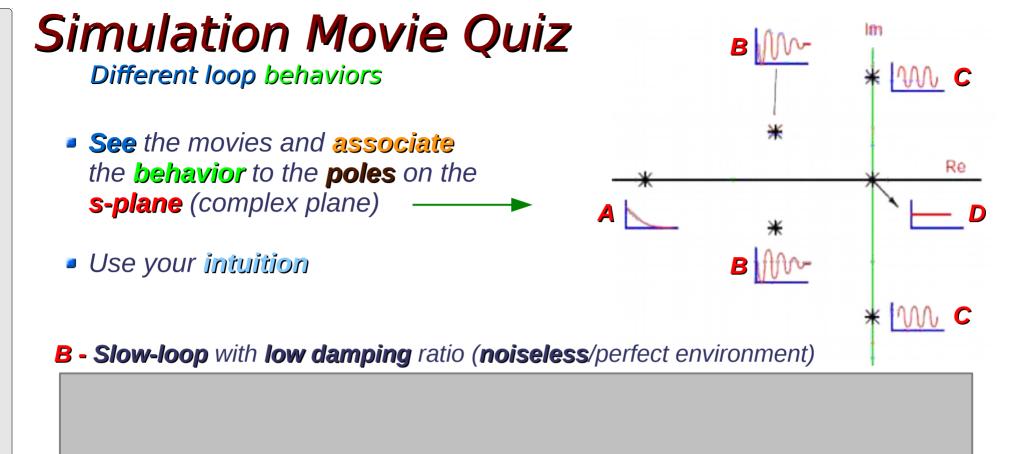




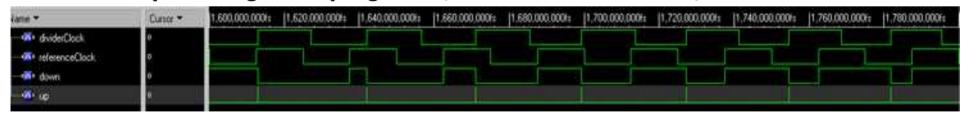
? - Fast-loop with high damping ratio (noiseless environment)



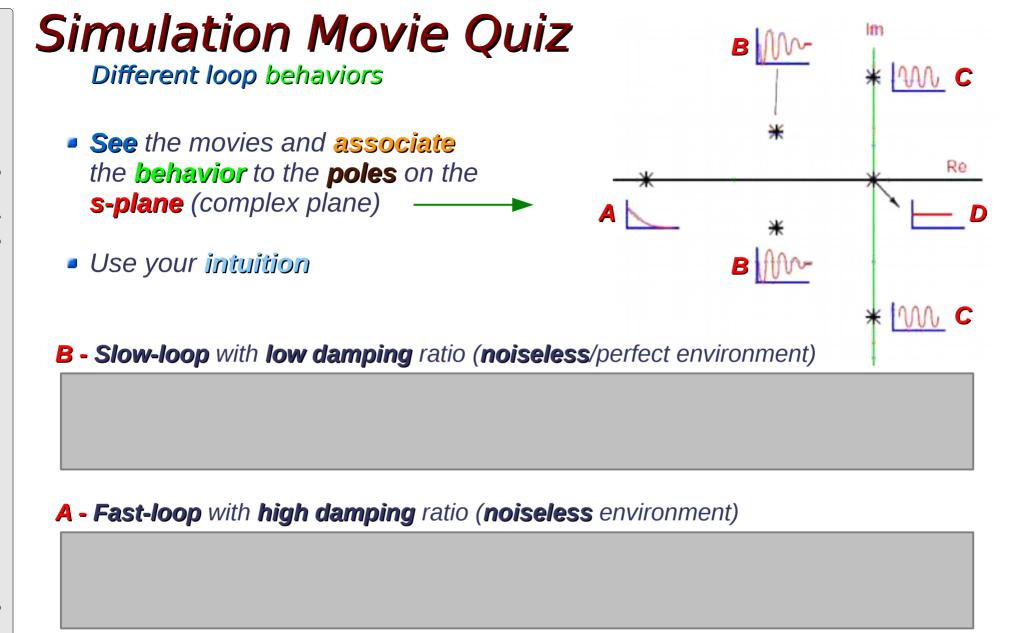
? - Slow-loop with low damping ratio (noisy environment)



? - Fast-loop with high damping ratio (noiseless environment)



? - Slow-loop with low damping ratio (noisy environment)



? - Slow-loop with low damping ratio (noisy environment)



# Back to the big picture

If the PLL fails, then nothing works !..

- In case the loop parametrization is wrong:
  - → PLL can not deliver a proper clock
    - → No phase/frequency locked ClkPLL signal
    - → Ignored LHC clock, no synchronization
  - → SER fails

RefClk

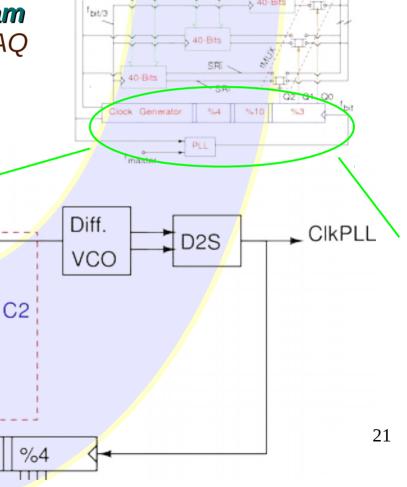
- Some of the bits get lost or duplicated
- High jitter leading to closed eye diagram
- → RO fails delivering the data from FE to DAQ

Up

Down

No DAQ → Fatal error !..

**PFD** 



DAO

master

Load

**LPF** 

C<sub>1</sub>

%30

3.6.9.

1.4.7.

FE FE FE

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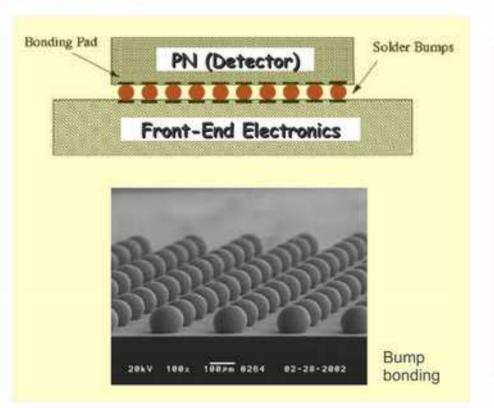
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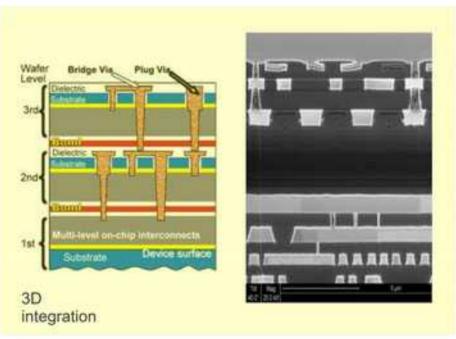
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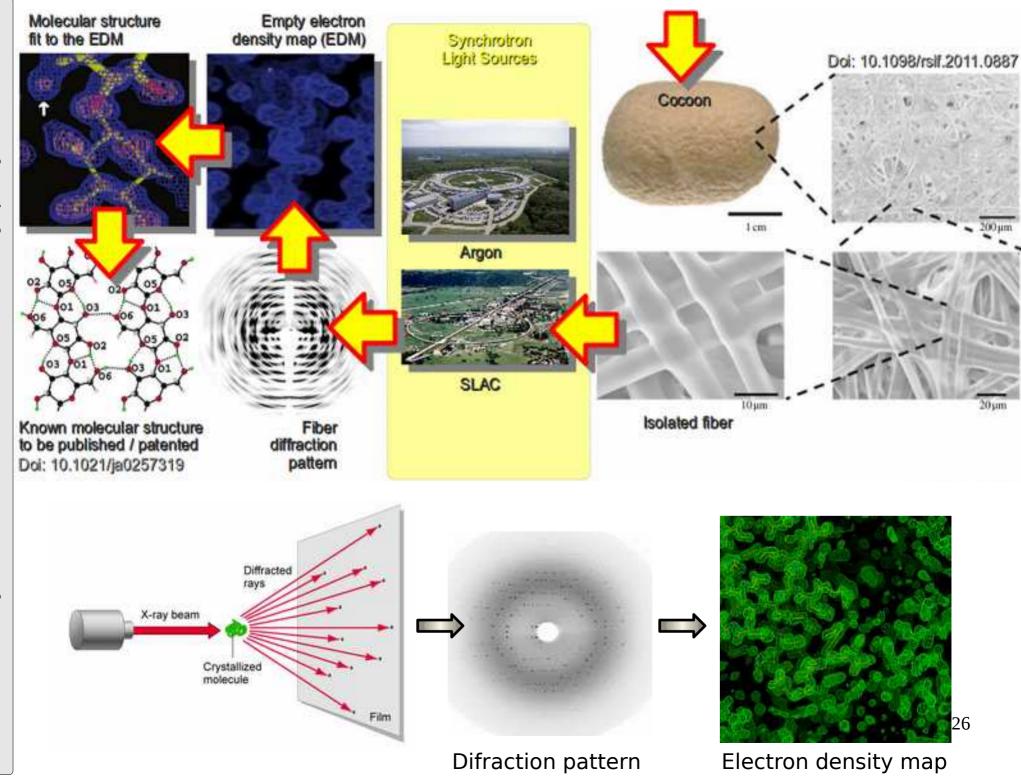
# An Example

### Pilatus System: A hybrid of "sensor + electronics"

- "The development at PSI is driven by the design of the pixel detector for the CMS (Compact Muon Solenoid) experiment at the planned Large Hadron Collider (LHC) at CERN." (Ref: http://pilatus.web.psi.ch/publications.htm)
- Hybrid: fully depleted detector sitting on top of the front end electronics, reading out the detector, integrated within each of the pixels
- Composed of the detector, charge-sensitive preamplifier, shaper, comparator and counter

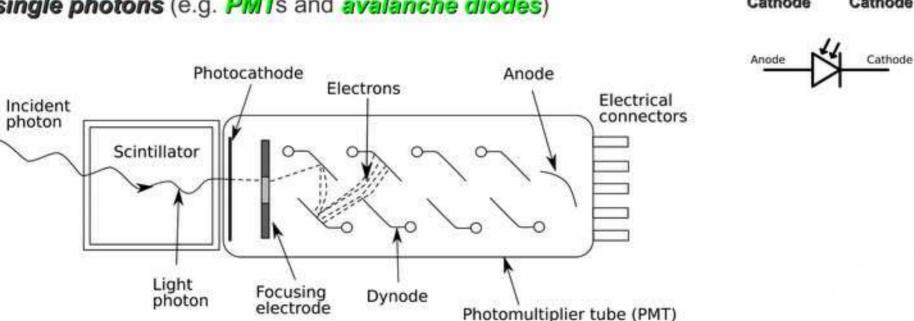


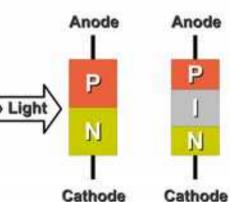




First interaction with the photons (and/or particles)

- Impossible to cover all
  - There are many types and even many more examples of particle detectors
- Therefore limited
  - Just a few types and examples should be enough, given the limited time
- "Seeing" the photons → photodetector != photon counter
  - Photo-detectors: generate an analog level (i.e. I or V) as a function of "light" intensity (e.g. PN and PIN structures)
  - Photon counters: count individual bursts of photon bundles or single photons (e.g. PMTs and avalanche diodes)





First interaction with the photons (and/or particles)

- Photo-detectors: generate an analog level (i.e. I or V) as a function of "light" intensity (e.g. PN and PIN structures)
- Two modes of operation:
  - Photo-voltaic mode
    - Depleted region is exposed to light and voltage is measured, with no bias
  - Photo-conductive mode
    - Exposed light generates a current flow, under reverse-bias
- Some important features:
  - Responsivity (I/P optic)
  - Active area
  - Max photo current (limited by saturation)
  - Dark current (in photoconductive mode)
  - Bandwidth (rise, fall times)
  - .
  - -



Photo-voltaic mode

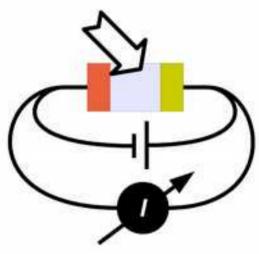
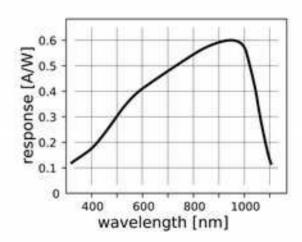
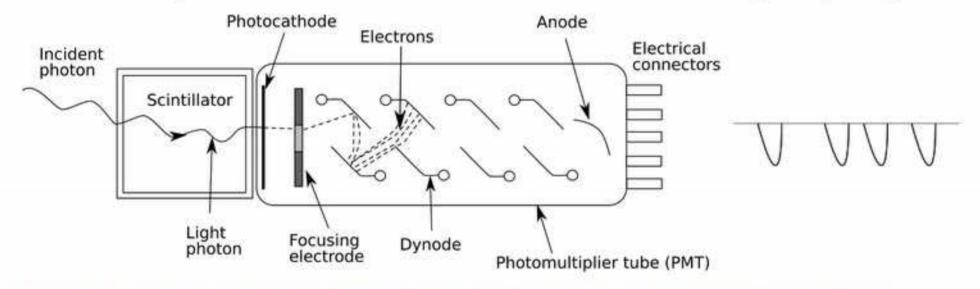


Photo-conductive mode

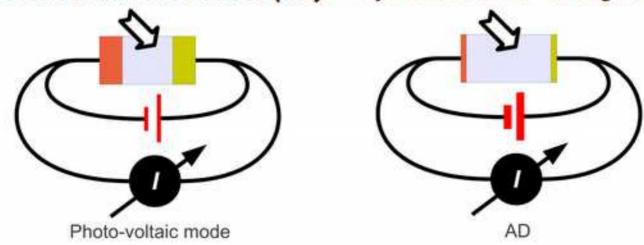


First interaction with the photons (and/or particles)

- Photon counters: count individual bursts of photon bundles or single photons (e.g. PMTs and avalanche diodes or SPADs)
  - Photomultipliers: if photons arrive at the detector with low-enough frequency

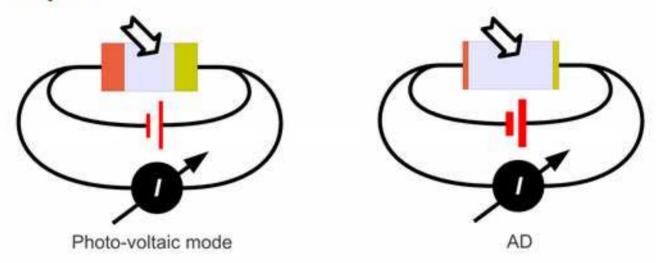


- Single Photon Avalanche Diodes (AD): PN junctions under strong reverse-bias



First interaction with the photons (and/or particles)

- Photon counters: count individual bursts of photon bundles or single photons (e.g. PMTs and avalanche diodes or SPADs)
  - Avalanche Diodes (AD) are PN junctions reverse-biassed just below the break-down voltage such that single-photon induced electrons are accelerated within a few µms



- Single-Photon Avalanche Diodes (SPAD) are PN junctions reverse-biassed just above the break-down voltage. When a photon strikes, bias voltage is droped down below the threshold (but not to break-down) for a short time (e.g. 100 ns) by carefully designed electronics to recover, such that the detector is ready for the next detection
- SPADs can also be used for time-resolved techniques as they can provide information on photons time of arrival in addition

# Position Sensitive Architecture

First interaction with the photons (and/or particles)

- Detect particles with the sensitivity of where they land; two main paradigms:
  - Resistive charge division on a single detection element:

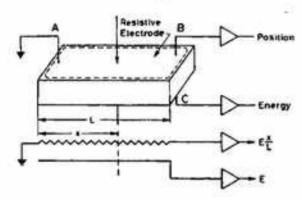
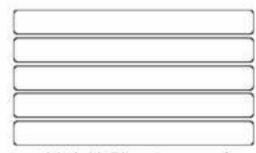


Fig. 10.14. Layout of a one-dimentional continuous position-sensitive detector using resistive charge divition. A simplified equivalent circuit is shown below

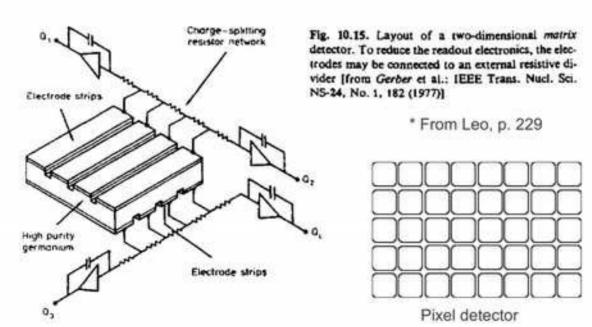
\* From Leo, p. 227

$$Position = \frac{B}{C}$$



A hybrid: Discrete array of resistive charge division

Discrete array of individual detection elements:

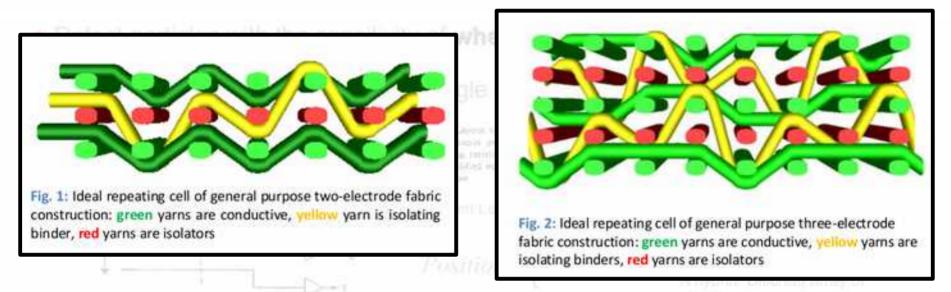


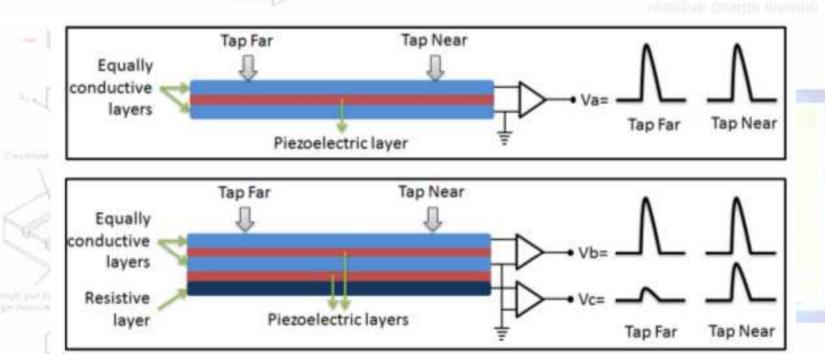


MEDIPIX

## Position Sensitive Architecture

First interaction with the photons (and/or particles)





# Time Resolved Architecture

read-out

signal

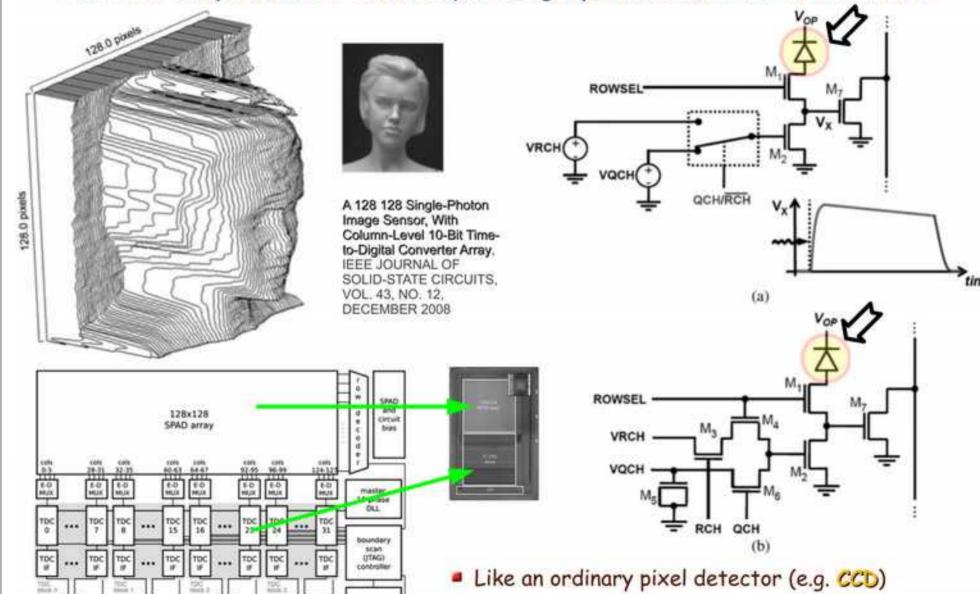
peneration

pipelined time-multiplexer

time multiplied TDC data

pad interfaces

Flash the sample, start a timer, acquire single photons and their arrival times



(e.g. TPC)

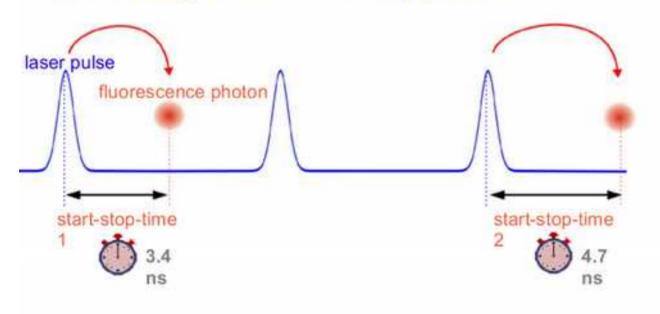
However measures "time" instead of "color"

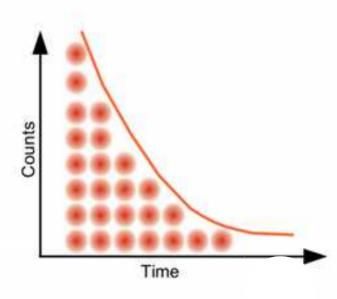
Generates 3D and color-less images

## Time Correlated Architecture

First interaction with the photons (and/or particles)

- Measuring the profile of a fast (e.g. fluorescence, from ps to ns) and/or weak decay is tricky
- Recovering not only the lifetimes but also the decay shape requires the decay to be represented by at least 10s of samples
- The idea:
  - Meet the single photon counting condition(?)
    - Make your detector fast
    - Decrease the number of photon creation at the source
  - Excite the system to be probed (e.g. via a laser)
  - Count photons per reference excitation
  - Fill a histogram to visualize decay profile





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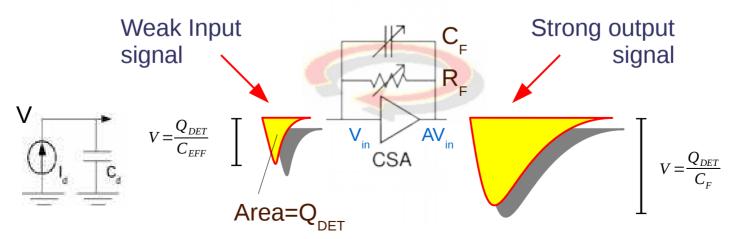
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# **Pre-Amplifier**

The first stage of the interpretation

- Standardized experimental techniques over time
- Our discussion on intuitive & descriptive level
- $T = \frac{V_{OUT}}{V_{IN}} = \frac{A}{1 + AB}$   $\begin{array}{c} sage: T(A, B) = A/(1 + A * B) \\ sage: T.limit(A = infinity) \\ (A, B) \mid --> 1/B \end{array}$

- Three types of pre-amplifiers:
  - → Voltage sensitive: usually not preferred due to the fact that, for a given amount of charge generated by the detector (Q<sub>DET</sub>), the output voltage of the detector (V) is a function of the effective capacitance (C<sub>EEE</sub>) of the detector which is variable
  - Current sensitive: not preferred because they are suitable to be used with low impedance devices, however radiation detectors have usually high impedance
  - Charge sensitive: preferred type because its output is only a function of the charge (Q<sub>DET</sub>) and a fixed C<sub>E</sub>, provided that amplifier gain is sufficiently high



out

# Amplifier Basic

How to amplify something

We want a small change in the input to cause a big change at the output

→ The **reason** it is called an amplifier

However in a real circuit, the input signal **dies** out, therefore:

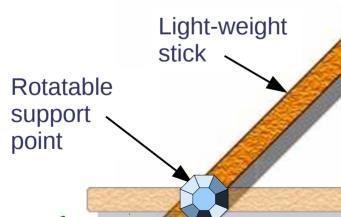
Output signal is a re-generated larger "clone"

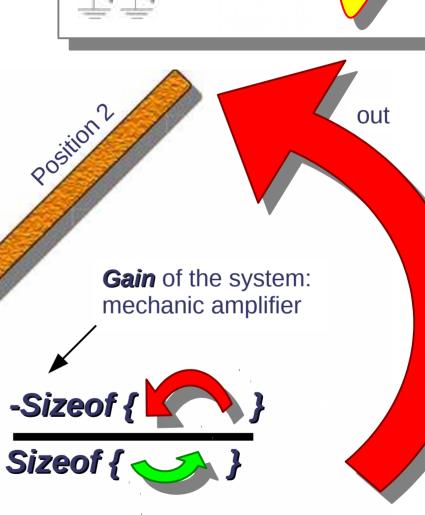
Output can have other features that the input did not

Gain=

Support

(the amplifier)





CSA

Weak

input

signal

Position 1

Strona

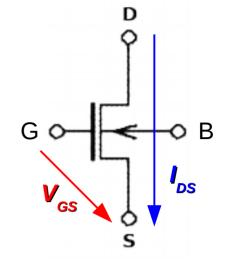
output

signal

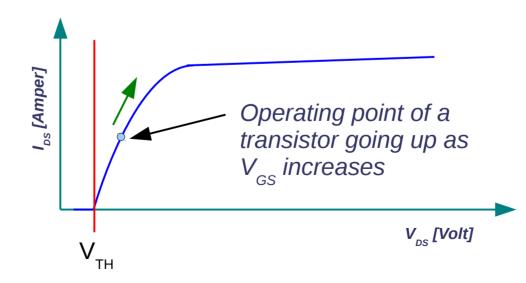
# Transconductance - $g_m$

Figure-or-merit for a transistor

- Define a figure-of-merit (FOM) for a single nMOS
  - → How well a transistor converts voltage into current
  - From input V<sub>GS</sub> to output I<sub>DS</sub>



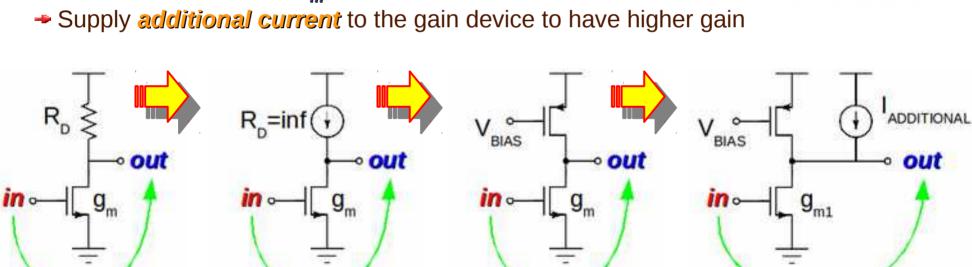
$$g_m = \frac{dI_{DS}}{dV_{GS}} = \frac{2I_D}{V_{GS} - V_{TH}}$$

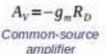


# Basic CMOS Amplifier

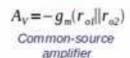
Single-stage common-source amplifier and its evolution into a complete circuit

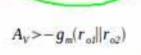
- Sink current through R<sub>p</sub>
  - → As in increases, out decreases (faster)
- -g<sub>m</sub>R<sub>D</sub> suggests that we should increase the load impedance to have higher voltage gain
  - → An ideal current source has infinite impedance
- A current mirror is a practical current source
  - Simply a transistor biased as a current source
- Transconductance  $(g_m)$  increases with current









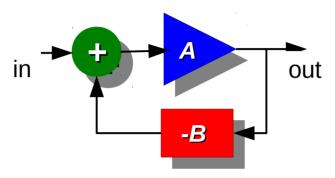


Common-source amplifier with current source load featuring higher gain due to increased current

# Basic CMOS Amplifier

Single-stage common-source amplifier and its evolution into a complete circuit

- Add the feedback network  $C_{\mathbf{r}} \& \mathbf{R}_{\mathbf{r}}$  forming the  $\mathbf{B}$  such that
  - $\rightarrow$  For high enough  $A_{\nu}$ , closed loop gain is 1/B

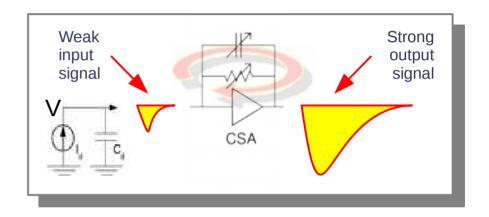


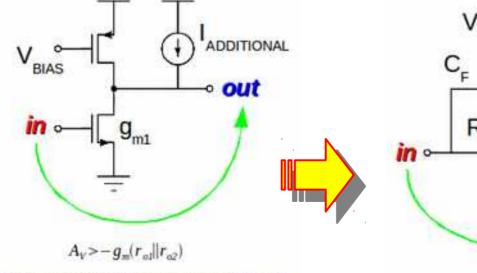
Common-source amplifier with current source load

featuring higher gain due to increased current

$$T = \frac{V_{OUT}}{V_{IN}} = \frac{A}{1 + AB}$$

$$\begin{array}{c} \text{sage: } T(A, B) = A/(1 + A * B) \\ \text{sage: } T.\text{limit}(A = \text{infinity}) \\ (A, B) \mid --> 1/B \end{array}$$

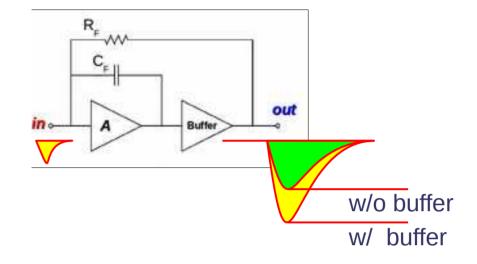


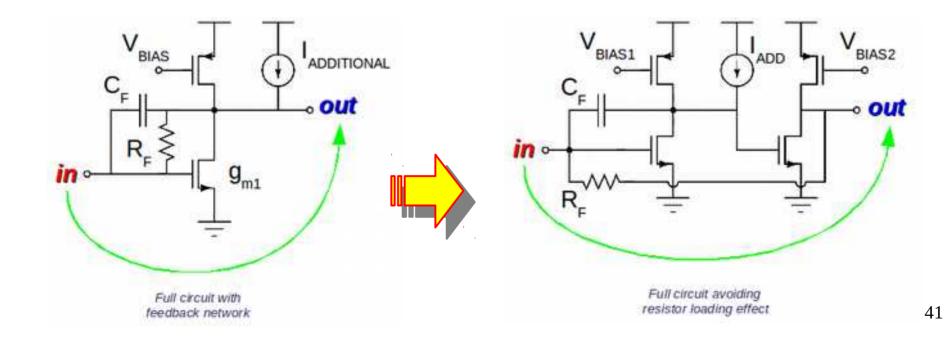


# Basic CMOS Amplifier

Avoid loading effect of the resetting resistor

- Problem: while c<sub>F</sub> is charged, R<sub>F</sub> resets at the same time
  - **Lowering** the voltage gain, therefore:
  - Loading effect of the feedback resistor should be avoided
  - Integration and resetting should be decoupled
  - Employing a buffer is one of the possible solutions

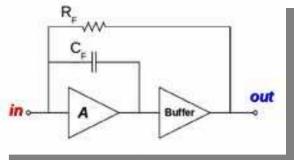


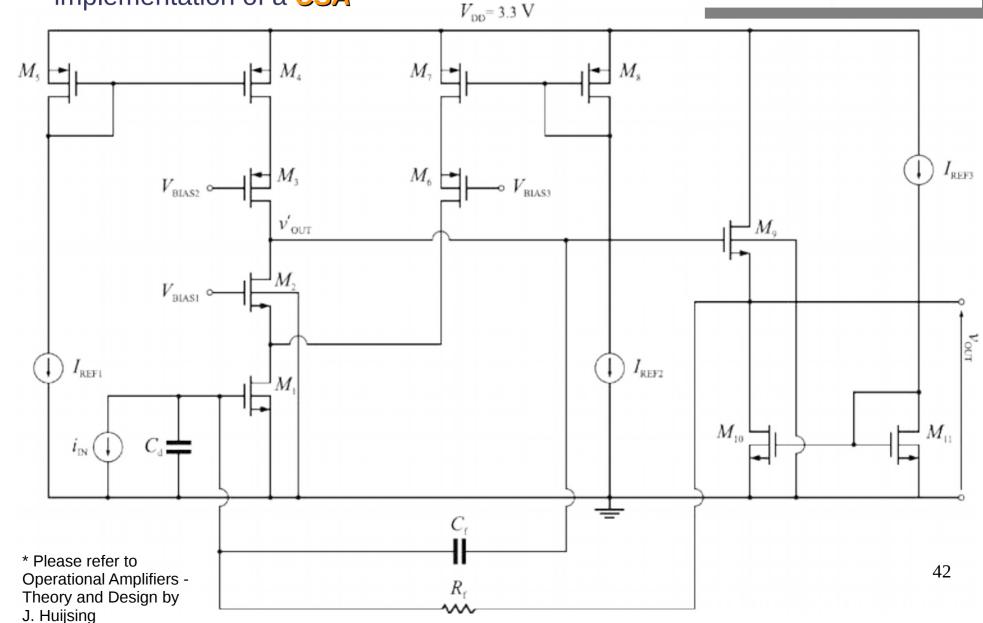


# **Pre-Amplifier**

Full circuit (currently in use at a RICH detector)

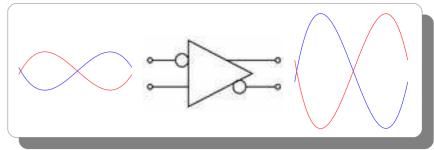
Actual CMOS device-level implementation of a CSA

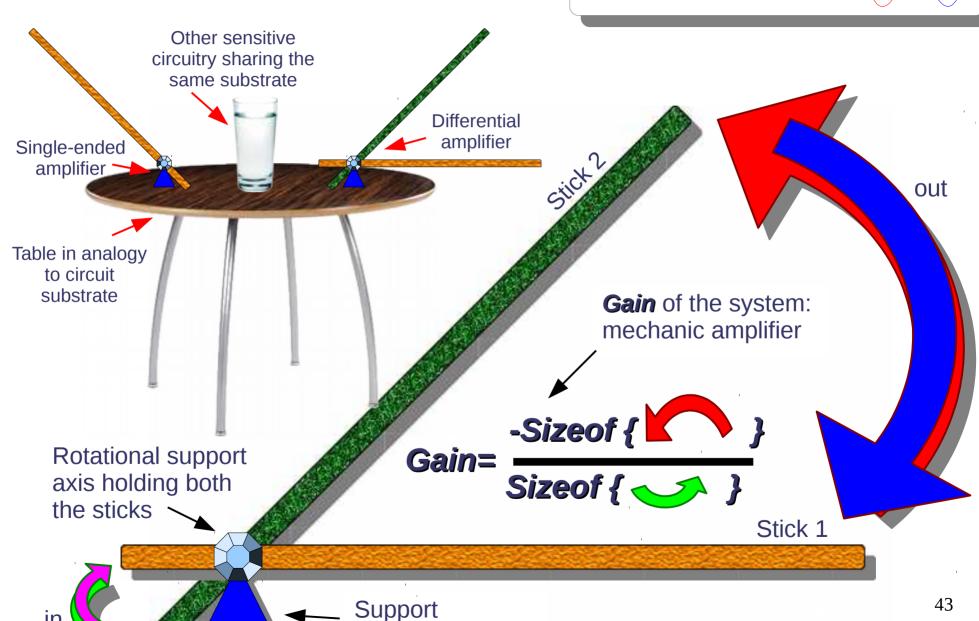




# Differential Amplifier

Generating less noise (also for others) in the cost of more complex design

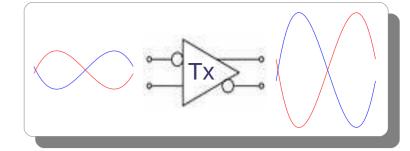




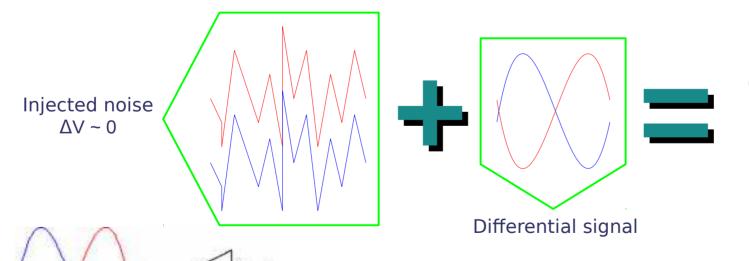
(the amplifier)

# Differential Signaling

Rejecting noise



- The information Tx generates is in the difference
  - Signal creates complementary current images on the substrate
  - Generating less noise for neighboring circuitry
- Rx compares the voltage levels of the pair
- Any noise source should affect both of the lines similarly
  - Generating almost identical transients on both of the wires
  - → Pair wires are close to each other
- Practically high noise rejection is feasible





Noise source (Ionizing particle passage, electronic noise injected by neighboring circuitry, etc.)



# Differential Signaling

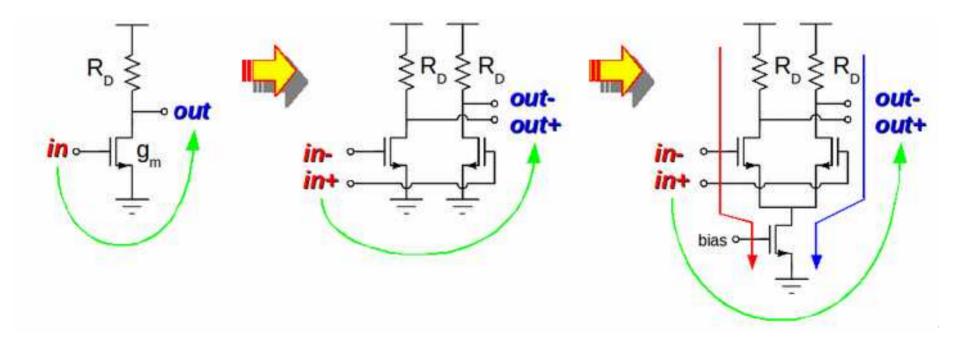
Differential gain stage

Sink current through R

- → As in increases, out decreases (faster)



- → Drawback: signals can be identical (no differential information)
- Steer the current either through one inverter or the other
  - → Transition at the input changes the path through which the current is steered
  - → Unless metastable, the amplifier has always differential information at he output





# Introduction to the Design of Full-Custom Front-End & Data Transmission ASICs\*

Table of Contents

### The Big (but Brief) Picture

- → Briefly front-end FE
- Briefly read-out RO
- Briefly serializer SER
- → Briefly phase-lock loop PLL

### Feed-Back Concept

- → A **qualitative** introduction
- Natural frequency concept ω
- Real-world examples:
  - Binary read-out
  - Time-over threshold
- Adjusting/optimizing loop behavior
  - Damping ratio

### Reminder on Detectors

- Photodetectors vs photon counters
- Position-sensitive detectors
  - Resistive charge division
  - Discrete array of elements
- Time-resolved detection

### Detector Front-End ASICs

- → Pre-Amp: basic idea V<sub>out</sub> / V<sub>IN</sub>
- Transconductance of a transistor g<sub>m</sub>
- Evolving a single-stage amplifier into a real-world application

### Processing Technology

- Transistor switch A masterpiece
  - Lithography
  - → Formation of an **nMOS** transistor
- VLSI design flow
  - Parasitic extraction
- Real-world ASIC examples

### Radiation Tolerance Issues

- Definitions:
  - Single event upset, analog single event transient, latch-up
- Simulating radiation effects on analog circuits

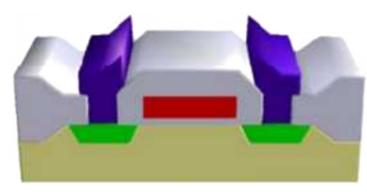
46

# Semiconductor Switch - Transistor

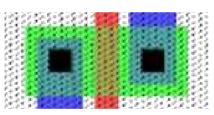
A masterpiece

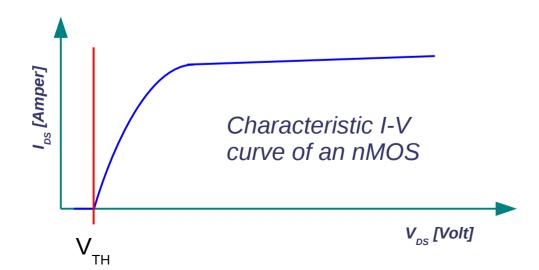
 Current conduction between Drain-Source as a function of Gate-Source voltage

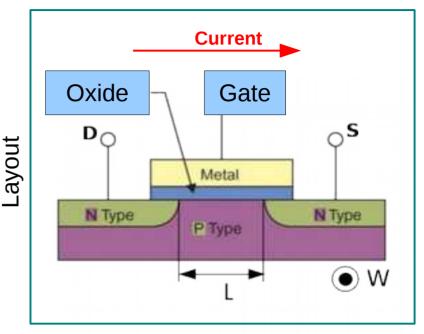
**3D view** of a single MOS transistor

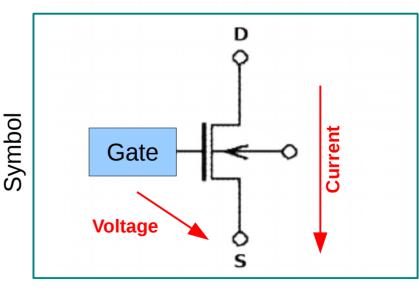


A single MOS transistor as drawn by a designer







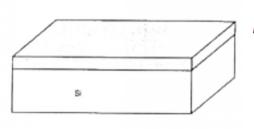


47

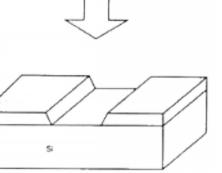
# Lithography

The art of light drawing

- A real microelectronic circuit is like a city composed of many layers
- A specific lithographic mask is needed for each layer to be created
- As an example we will create a "line" on an oxide layer



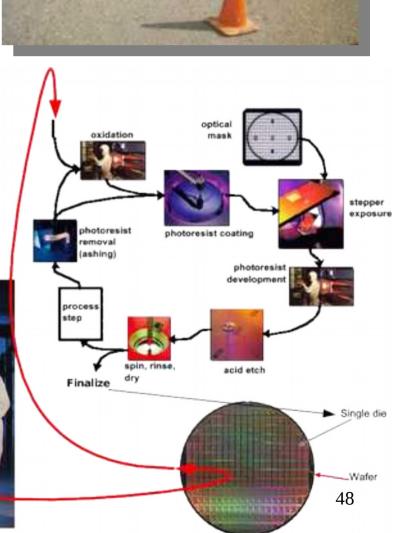
Initial state



Target

The *ingot* to be sliced into *wafers* 



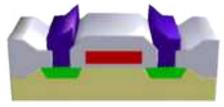


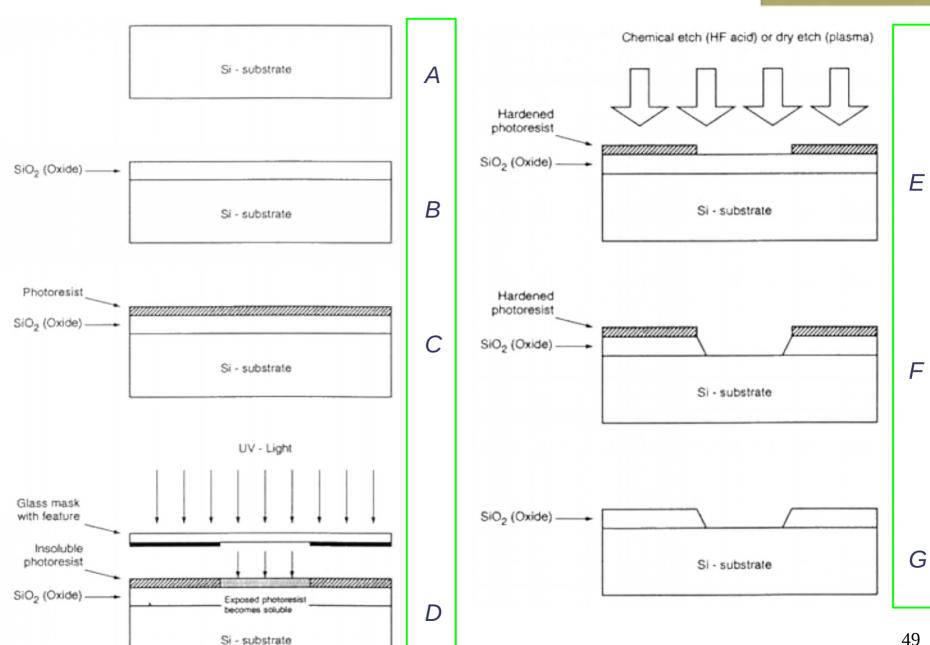
<sup>\*</sup> Please refer to Semiconductor Devices: Physics and Technology by S. M. Sze

# Design of Low-Level Front-End and Data Transmission ASICs - Özgür Çobanoğlu

# Just to draw a single line

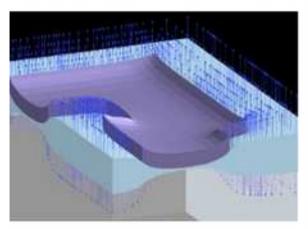
Seven simplified steps

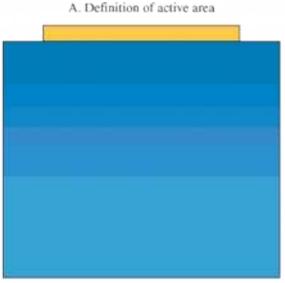


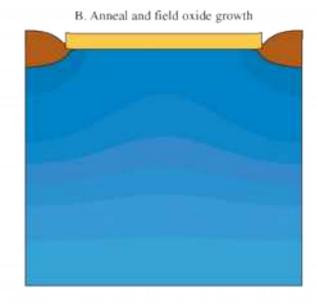


# Fabrication of an nMOS

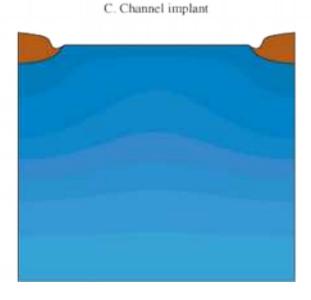
Simplified steps - Part I

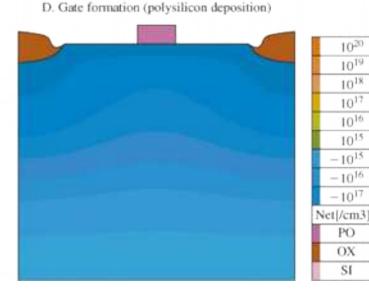






- Nitride defines the active areas
- FOX is developed
- Nitride is removed by a solvent
- Polysilicon is deposited

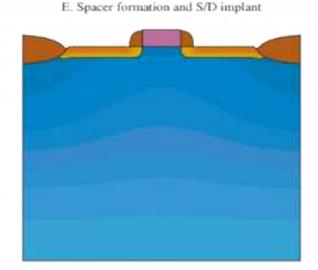


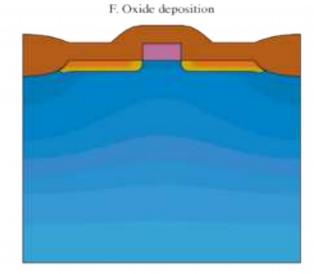


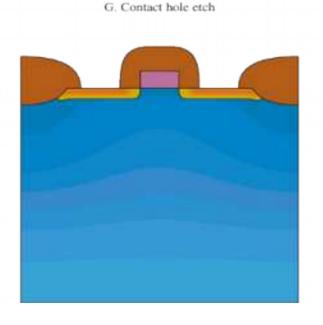
# Fabrication of an nMOS

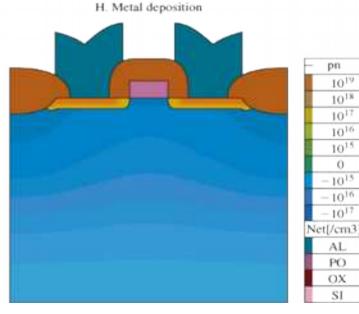
Simplified steps - Part II

- Spacer & active field formation
- Dep. of SiO<sub>2</sub>
- Etching contact holes
- Metal dep.



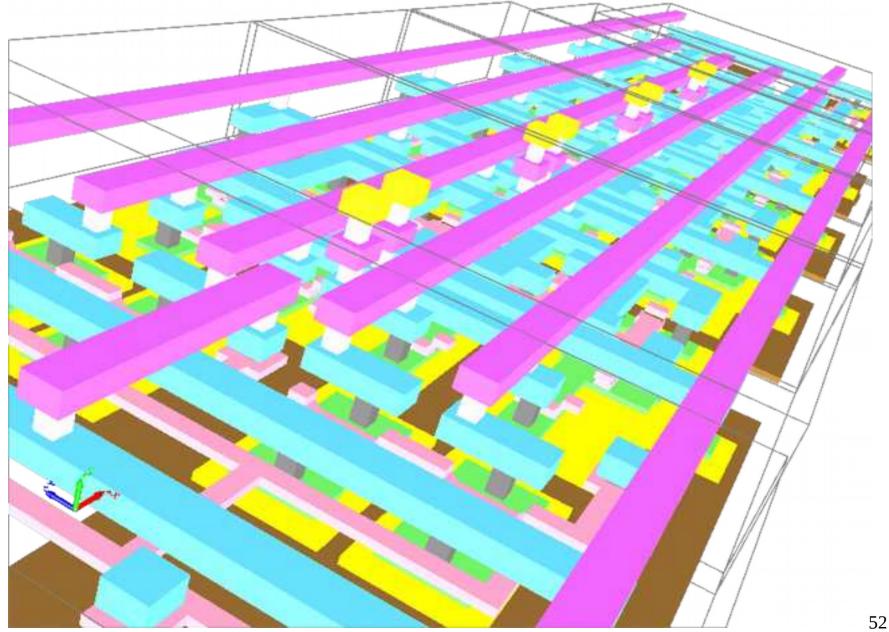






# How many layers do you see ?

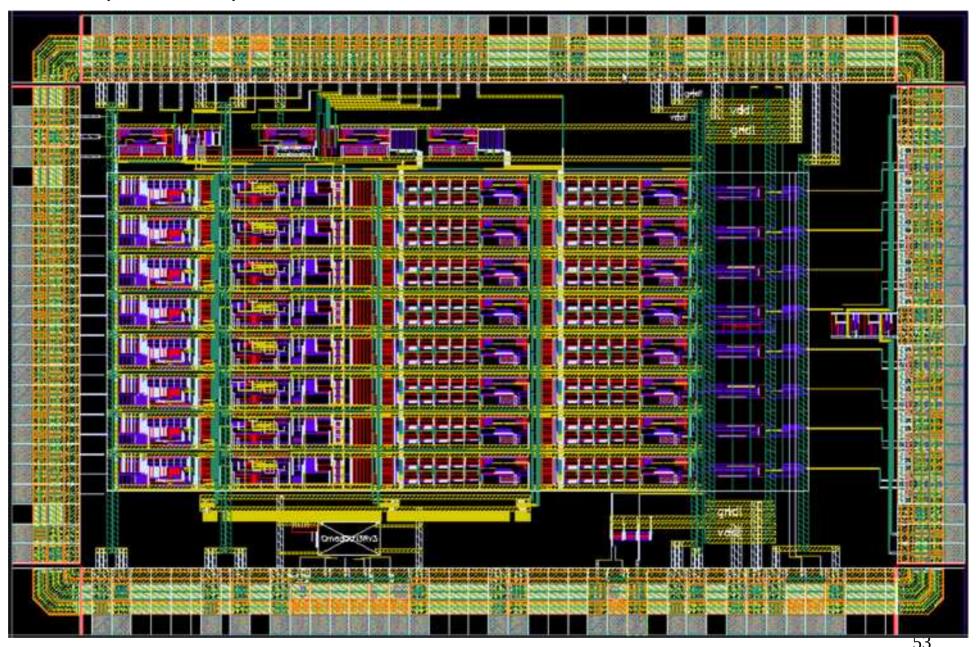
A process repeated a few hundred times



A ring-type oscillator

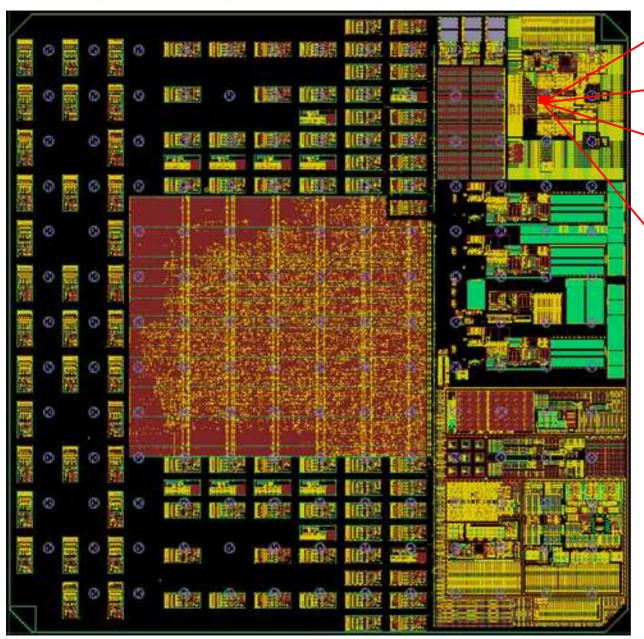
# How many layers do you see ?

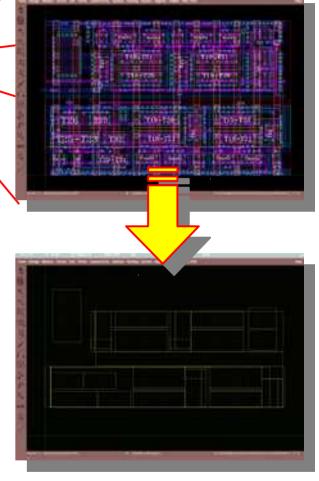
A process repeated a few hundred times



# How many layers do you see?

A process repeated a few hundred times





A sub-set of masks forming the above block (Animated GIF image)

The first prototype of the SER-DES ASIC for the GBT13 chip-set under development for the Super-LHC at CERN. (130 nm CMOS)

# VLSI Design in Practice

7.2.a

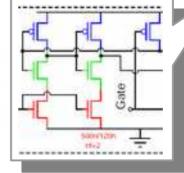
9.2.a

Daily life of an ASIC designer

Interface between process scientist and designer

Focus on **reliability** and increased manufacturability

T(a) =	$\omega_n^2(\tau s + 1)$
I(s) =	$\frac{\overline{s^2}}{N} + 2\xi s \frac{\omega_n}{N} + \frac{{\omega_n}^2}{N}$



Converter

## Layout

**Specifications** 

Schematic entry

Simulation

Design Rule Check

**Parasitic Extraction** 

Layout Versus Schematic check

> Post-Layout Simulation

### Contact

5.1	Exact contact size	2 λ
5.2	Min. poly overlap	1.5 A
5.3	Min. spacing	2 λ
5.4	Min. spacing to gate	2 λ
6.1	Exact contact size	2 λ
6.2	Min. active overlap	1.5 λ
6.3	Min. spacing	2 λ
6.4	Min spacing to gate	2.)

### Metal 1

7.1	Min. width	3 )
7.2.a	Min. spacing	3 )
7.3	Min, overlap of any contact	1. \( \lambda \)

### Via1

8.1	Exact size	2 λ
8.2	Min. spacing	3 λ
8.3	Min. overlap by metal1	$1 \lambda$
8.4	Min. spacing to contact	$2\lambda$
8.5	Min. spac. to poly or act. edge	$2\lambda$

### Metal2

9.1	Min. width	3 λ
9.2.a	Min. spacing	4 λ
9.3	Min. overlap to via1	1 λ

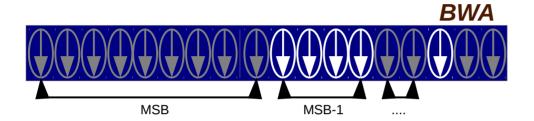
(\*) Not Drawn

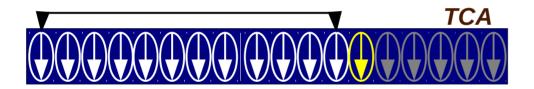
### Architectural Choice

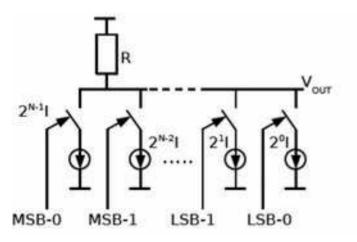
Quantitative comparison between different approaches

**Specifications** 

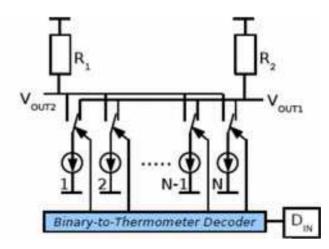
- ◆ A 10-Bit current-mode D/A converter
- Two possible architectures; have to choose one
- Need for qualitative comparison: MC is a must



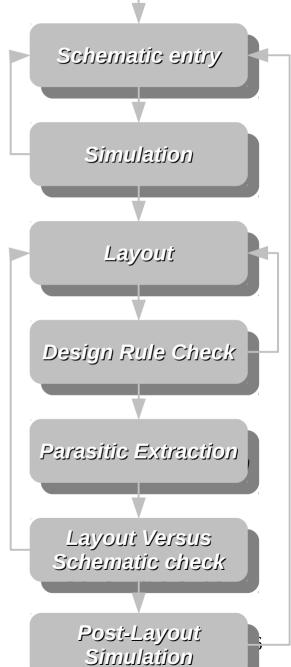




Binary weighted (BWA)

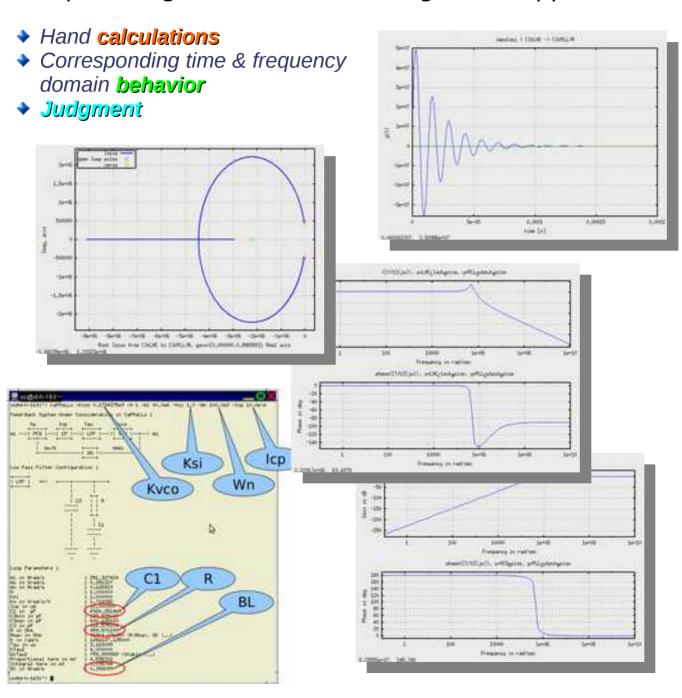


Thermometer coded (TCA)

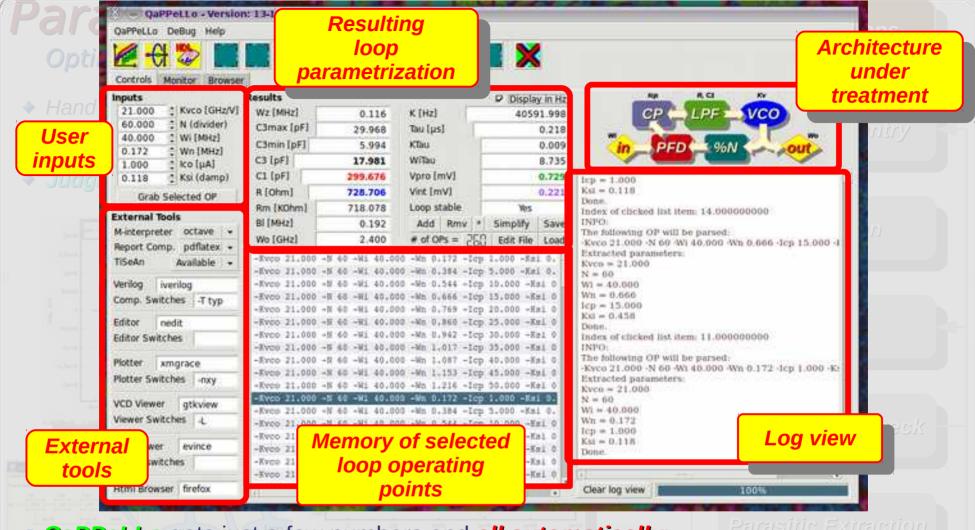


## **Parametrization**

### Optimizing the choice according to the application

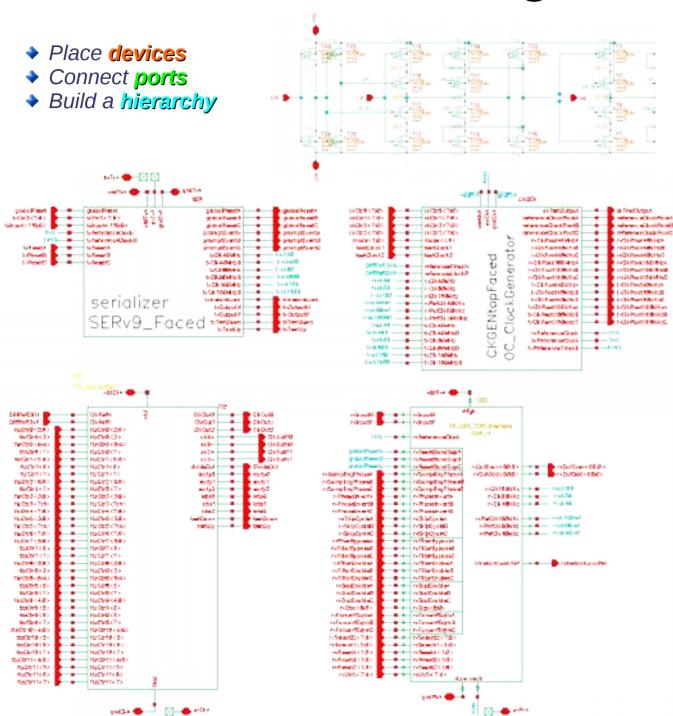


**Specifications** Schematic entry Simulation Layout Design Rule Check Parasitic Extraction Layout Versus Schematic check Post-Layout Simulation



- CaPPeLLo gets just a few numbers and all automatically:
  - Calculates loop parameters and generates the stability map for comparison
  - Calculates frequency domain loop response as
    - Bode and root locus plots, step & impulse responses, noise transfer functions, etc.
  - Generates the verilog model of the architecture with the selected parameters
    - Compiles and runs the verilog model, displays the wave forms
    - Analyzes the jitter data generated during the this simulation
  - Searches for chaos by means of time series analysis and creates attractors, etc.
  - Generates a report summarizing all above actions

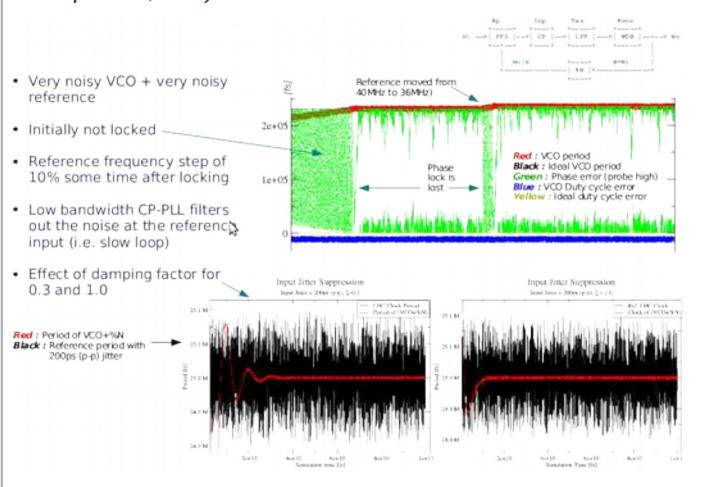
# Schematic-Level Design

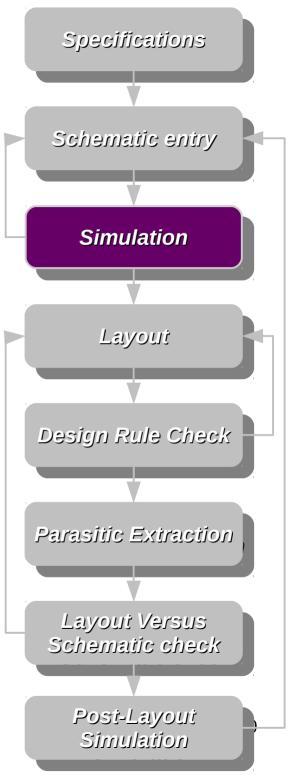


Specifications Schematic entry Simulation Layout Design Rule Check Parasitic Extraction Layout Versus Schematic check Post-Layout Simulation

# Simulation

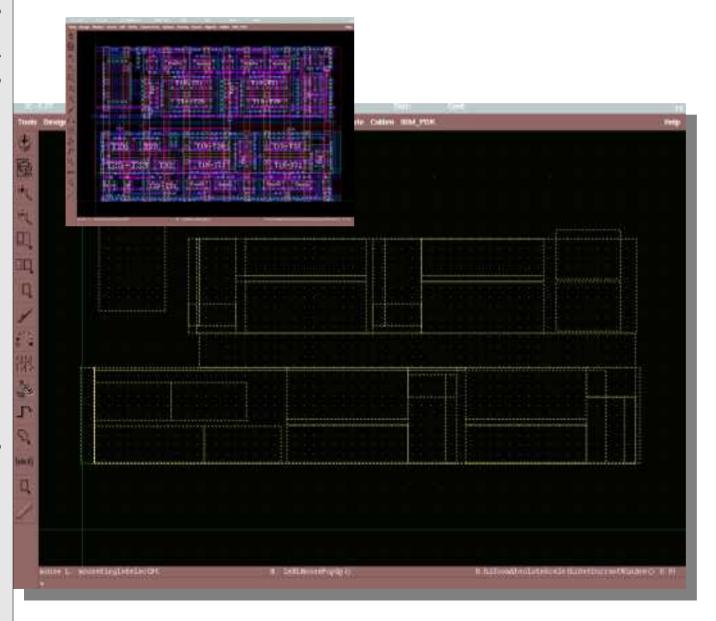
- Model-based time-step simulations (HDLs, MatLab, Octave, Cadence, etc.)
- → Transistor-level SPICE simulations (Spectre, UltraSim, etc.)
- Radiation simulations (Process simulators, Spectre, etc.)

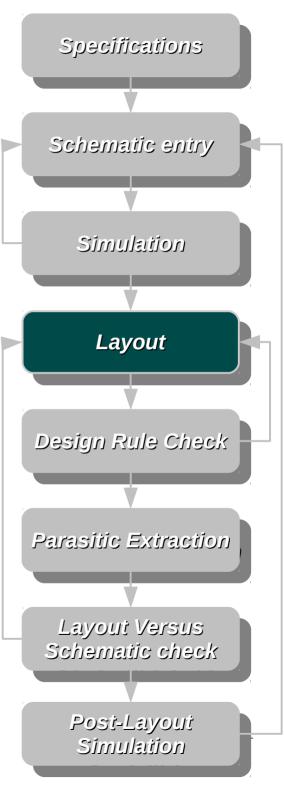




# Layout

- Lithographic masks are designed
- Actual representation of a circuit on the die



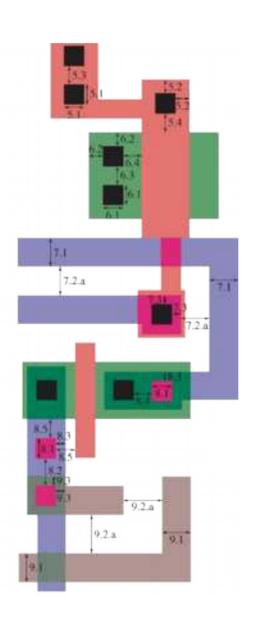


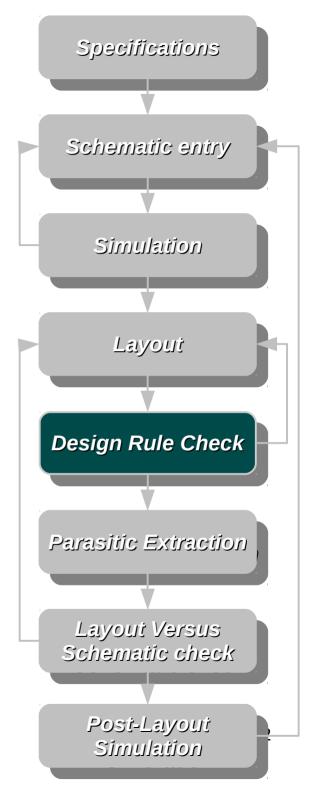
# **DRC**

◆ Infinite different paths of matching what the schematic represent (art)

Co	ntact	
5.1	Exact contact size	$2\lambda$
5.2	Min. poly overlap	1.5 A
5.3		$-2\lambda$
5.4	Min. spacing to gate	2 λ
6.1	Exact contact size	2 λ
6.2	Min. active overlap	1.5 A
6.3	Min. spacing	$2\lambda$
6.4	Min. spacing to gate	2 λ
Me	etal 1	
	Min. width	3 λ
7.2	a Mia enacina	
	2.a Min. spacing 3. Min. overlap of any contact	
	Min, overlap of any contact	
7.3	Min, overlap of any contact	1 λ
7.3 Via 8.1	Min. overlap of any contact  Exact size	1 λ
7.3 Via	Min. overlap of any contact  Exact size Min. spacing	2 A
Via 8.1 8.2	Min. overlap of any contact  Exact size Min. spacing Min. overlap by metal 1	2 A 3 A 1 A
Via 8.1 8.2 8.3	Min. overlap of any contact  Exact size Min. spacing Min. overlap by metal I Min. spacing to contact	2 A 3 A 1 A 2 A
Via 8.1 8.2 8.3 8.4 8.5	Min. overlap of any contact  Exact size Min. spacing Min. overlap by metal I Min. spacing to contact	2 A 3 A 1 A 2 A
Via 8.1 8.3 8.4 8.5	Min. overlap of any contact  Exact size Min. spacing Min. overlap by metal I Min. overlap by metal I Min. spacing to contact Min. spac. to poly or act. edge	2 \( \lambda \) 3 \( \lambda \) 1 \( \lambda \) 2 \( \lambda \) 2 \( \lambda \) 2 \( \lambda \) 3 \( \lambda \
Via 8.1 8.3 8.4 8.5 Me	Min. overlap of any contact  Exact size Min. spacing Min. overlap by metal I Min. spacing to contact Min. spac. to poly or act. edge	2 \( \lambda \) 3 \( \lambda \) 1 \( \lambda \) 2 \( \lambda \) 2 \( \lambda \) 2 \( \lambda \)

Not Drawn



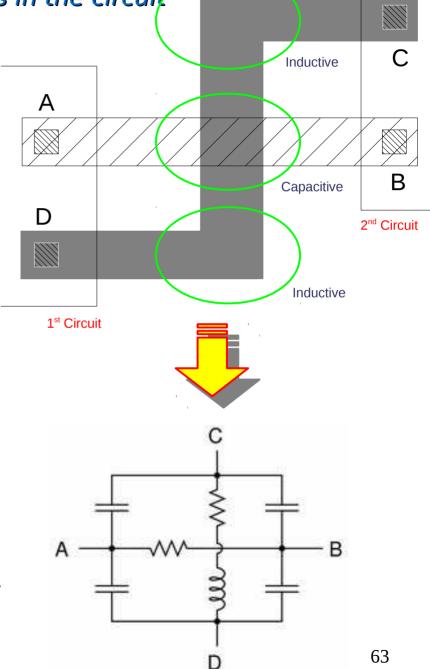


# Parasitic Extraction

For a better physical representation of what is in the circuit

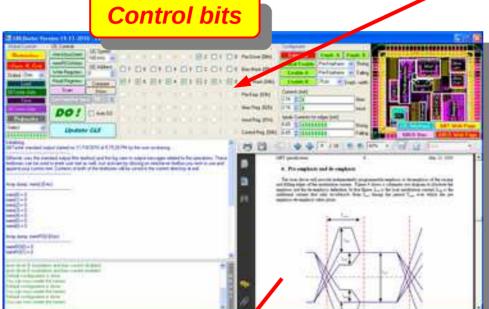


- Connect the pin A to pin B with metal-1
- → Connect the pin C to pin D with metal-2
- Designer did not draw any device but the effective circuit has at least the followings:
  - 4 capacitors
  - 2 resistors
  - → 1 inductor
- Things which are not taken into account in schematic are the parasitic devices that can not be avoided but minimized/maximized
  - e.g. minimize input capacitance of a FE or wire capacitances between building blocks
  - → e.g. maximize narrow-band PLL filter capacitance or de-coupling capacitors of any ASIC



# Test Boards

and tester/configurator application



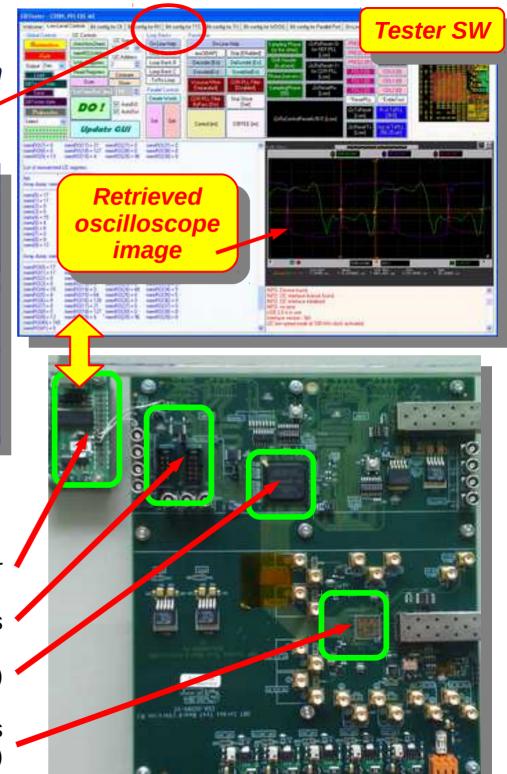
On-line documentation

USB → I2C adapter

I2C & JTAG ports

FPGA (Cyclon-III)

Where the DUT resides (DUT: Device Under Test)



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### Feed-Back Concept

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- Natural frequency concept ω<sub>n</sub>
- Real-world examples:
  - Binary read-out
  - Time-over threshold
- Adjusting/optimizing loop behavior
  - Damping ratio

### Reminder on Detectors

- Photodetectors vs photon counters
- Position-sensitive detectors
  - Resistive charge division
  - Discrete array of elements
- Time-resolved detection

### Detector Front-End ASICs

- → Pre-Amp: basic idea V<sub>out</sub> / V<sub>IN</sub>
- Transconductance of a transistor g<sub>m</sub>
- Evolving a single-stage amplifier into a real-world application

### Processing Technology

- Transistor switch A masterpiece
  - Lithography
  - → Formation of an **nMOS** transistor
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  - Parasitic extraction
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### Radiation Tolerance Issues

- Definitions:
  - Single event upset, analog single event transient, latch-up
- Simulating radiation effects on analog circuits

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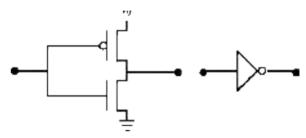
# Radiation Issues

### Definitions and failure mechanism

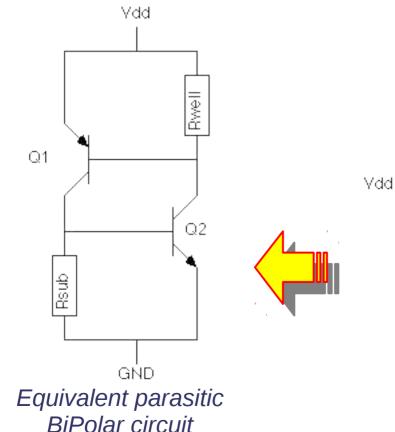
- Single Event Transient (SET)
  - → A transient perturbation on an analog signal due to charge released by an ionizing radiation.
- Single Event Upset (SEU)
  - → State change of a digital circuit due to charge released by an ionizing radiation.

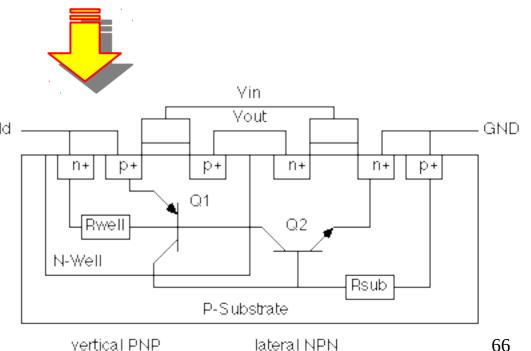
### Latch-Up

→ Creation of a low-resistance path between Vdd and Gnd due to a positive feedback loop formed by parasitic devices.

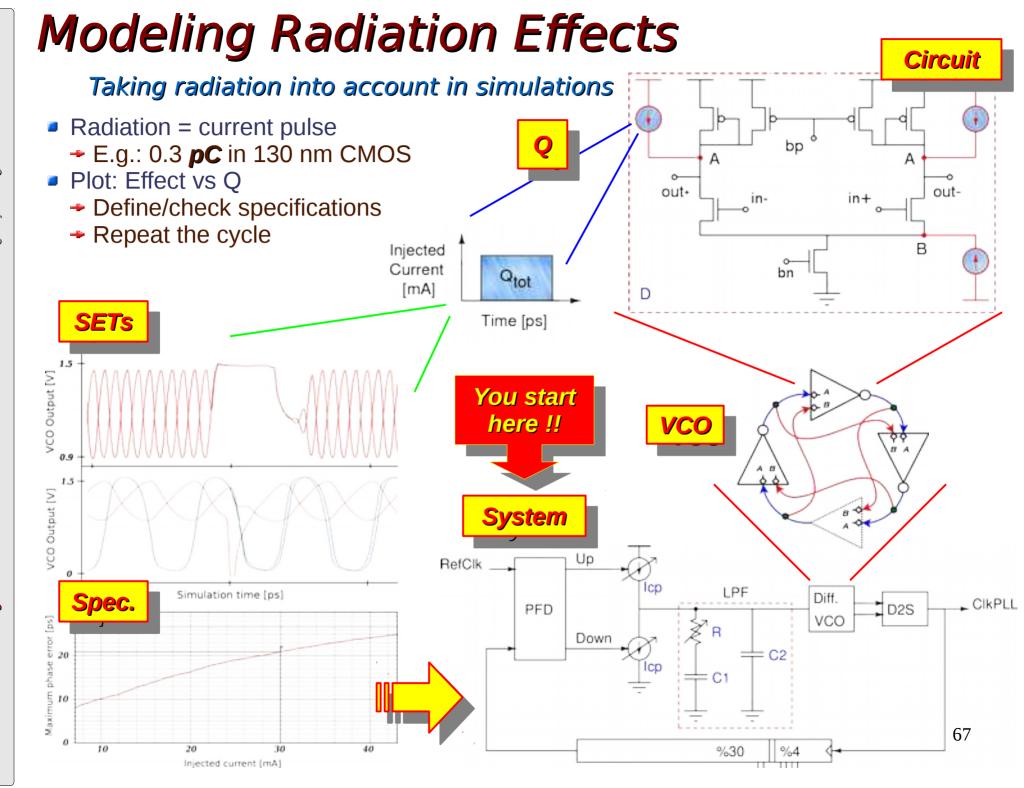


CMOS inverter and its symbol





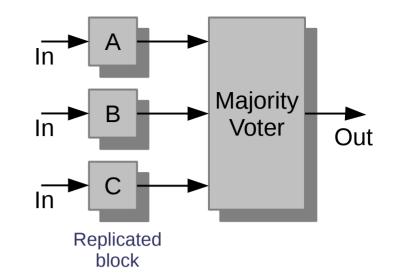
Wafer cross-section of the inverter

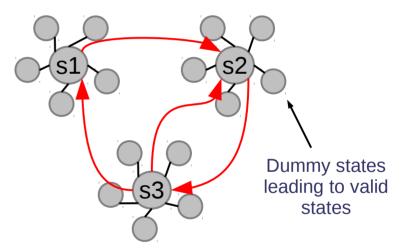


# Rad-Hard Design Tricks

### Adding robustness to circuits

- Use higher current levels and/or larger devices
  - The current/voltage excursions ionizing particles generate stay insignificant
  - → Prise to pay: increased circuit footprint and power dissipation, slower operation, etc.
- Use triple-well and/or guard-ring structures frequently
  - → To ground any noise before it reaches to sensitive circuitry
- Use Modular Redundancy (nMR)
  - Replicate circuitry and vote at the output, Triple Modular Redundancy (TMR) is commonly used
  - → The probability for an ionizing particle to affect all the three blocks at the same time is very low, therefore this technique is commonly used to harden designs against SEU





- Use dummy states to protect Finite State Machines (FSM) against SEUs
  - → If a state change occurs due to an ionizing particle passage, the FSM can return to a valid state without impairing
  - → Prise to pay: more complex FSM design, increased power dissipation and circuit footprint
- Place the ASICs within magnet **shadows** (where applicable)
  - → To decrease radiation tolerance requirements

# Introduction to the Design of Full-Custom Front-End & Data Transmission ASICs\*

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### The Big (but Brief) Picture

- → Briefly front-end FE
- Briefly read-out RO
- → Briefly serializer SER
- → Briefly phase-lock loop PLL

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